

Author index

- Abdesselam, M., see Chibani
- Abstreiter, G., Micro-Raman spectroscopy for characterization of semiconductor devices 50 (1991) 73
- Adams, P.M., see Moss
- Adriaenssens, G.J., see Usala
- Amarger, V., C. Dubon-Chevallier, A.C. Papadopoulos, B. Descouts and Y. Gao, Correlated use of characterization techniques to optimize the Mg implantation annealing for self-aligned HBT's 50 (1991) 462
- Ammerlaan, C.A.J., see Heijmink Liesert
- Ammerlaan, C.A.J., see Van Gisbergen
- Anderson, F.G., see O'Connor
- Anderson, M.A., see Woolf
- Anderson, T., see Deneuveville
- Antolini, A. and C. Lamberti, Computing errors in Fourier transform photoluminescence 50 (1991) 212
- Ardelean, I., see Gao
- As, D.J., see Wang
- Asakura, H., see Ohnishi
- Ashenford, D., J.H.C. Hogg, B. Lunn and C.G. Scott, The relationship between electrical and structural characteristics of CdTe and CdMnTe layers grown on InSb 50 (1991) 440
- Astles, M.G., see Keir
- Auret, F.D., see Bredell
- Austin, R.F., see Donegan
- Auvray, P., A. Poudoulec, M. Baudet, B. Guenais, A. Regreny, C. d'Anterrosches and J. Massies, Interface roughness of GaAs/AlAs superlattices MBE-grown on vicinal surfaces 50 (1991) 109
- Ayyub, P., see Deneuveville
- Bairamov, B.H., V.A. Voitenko, I.P. Ipatova, V.V. Toporov, G. Irmer, J. Monecke and E. Jahne, Characterization of III-V compounds by quasi-elastic electronic scattering of light 50 (1991) 300
- Baraldi, A., C. Ghezzi, A. Parisini, A. Bosacchi and S. Franchi, Analysis of electron mobility versus temperature after photoexcitation in Si-doped $\text{Al}_x\text{Ga}_{1-x}\text{As}$ 50 (1991) 405
- Baranovskii, S.D., Theoretical basis for the quantitative characterization of impurities in n-type III-V compound semiconductors by photoelectromagnetic spectroscopy 50 (1991) 218
- Barba, M.F., see Fariñas
- Barnard, W.O., see Bredell
- Barnett, S.J., see Keir
- Barnett, S.J., see Lee
- Baudet, M., see Auvray
- Bauer, J.G., R. Treichler, T. Hillmer, J. Müller and G. Ebbinghaus, Optimization of Zn dopant profiles in a pin-diode/FET by combination of depth profiling techniques: a SIMS, ECV and AES study 50 (1991) 138
- Baumgartner, M. and K. Löhnert, Characterization of si-GaAs wafer quality by room-temperature photoluminescence 50 (1991) 222
- Baurichter, A., M. Deicher, S. Deubler, D. Forkel, J. Meier, H. Wolf, W. Wittmann and ISOLDE Collaboration, Microscopical studies at cadmium impurities in compound semiconductors 50 (1991) 165
- Bausier, E., see Strasser
- Benchiguer, T., E. Christoffel, A. Goltzené, B. Mari, B. Meyer and C. Schwab, Donor-acceptor charge transfers in bulk semi-insulating GaAs as revealed by photo-EPR 50 (1991) 277
- Bender, G., see Herres
- Benyattou, T., see Roura
- Besland, M.P., see Tardy
- Besson, M., see Strasser
- Biglari, B., see Hage-Ali
- Blunt, R., see Pickering
- Bonnet, A., see Morsli
- Bosacchi, A., see Ghezzi
- Bosacchi, A., see Baraldi
- Boudart, B., B. Prévot and C. Schwab, Free-carrier concentration in n-doped InP crystals determined by Raman scattering measurements 50 (1991) 295
- Bowman, Jr., R.C., see Moss
- Brandstättner, M., see Sartorius
- Brec, R., see Morsli

Author index

- Abdesselam, M., see Chibani
- Abstreiter, G., Micro-Raman spectroscopy for characterization of semiconductor devices 50 (1991) 73
- Adams, P.M., see Moss
- Adriaenssens, G.J., see Usala
- Amarger, V., C. Dubon-Chevallier, A.C. Papadopoulos, B. Descouts and Y. Gao, Correlated use of characterization techniques to optimize the Mg implantation annealing for self-aligned HBT's 50 (1991) 462
- Ammerlaan, C.A.J., see Heijmink Liesert
- Ammerlaan, C.A.J., see Van Gisbergen
- Anderson, F.G., see O'Connor
- Anderson, M.A., see Woolf
- Anderson, T., see Deneuveville
- Antolini, A. and C. Lamberti, Computing errors in Fourier transform photoluminescence 50 (1991) 212
- Ardelean, I., see Gao
- As, D.J., see Wang
- Asakura, H., see Ohnishi
- Ashenford, D., J.H.C. Hogg, B. Lunn and C.G. Scott, The relationship between electrical and structural characteristics of CdTe and CdMnTe layers grown on InSb 50 (1991) 440
- Astles, M.G., see Keir
- Auret, F.D., see Bredell
- Austin, R.F., see Donegan
- Auvray, P., A. Poudoulec, M. Baudet, B. Guenais, A. Regreny, C. d'Anterrosches and J. Massies, Interface roughness of GaAs/AlAs superlattices MBE-grown on vicinal surfaces 50 (1991) 109
- Ayyub, P., see Deneuveville
- Bairamov, B.H., V.A. Voitenko, I.P. Ipatova, V.V. Toporov, G. Irmer, J. Monecke and E. Jahne, Characterization of III-V compounds by quasi-elastic electronic scattering of light 50 (1991) 300
- Baraldi, A., C. Ghezzi, A. Parisini, A. Bosacchi and S. Franchi, Analysis of electron mobility versus temperature after photoexcitation in Si-doped $\text{Al}_x\text{Ga}_{1-x}\text{As}$ 50 (1991) 405
- Baranovskii, S.D., Theoretical basis for the quantitative characterization of impurities in n-type III-V compound semiconductors by photoelectromagnetic spectroscopy 50 (1991) 218
- Barba, M.F., see Fariñas
- Barnard, W.O., see Bredell
- Barnett, S.J., see Keir
- Barnett, S.J., see Lee
- Baudet, M., see Auvray
- Bauer, J.G., R. Treichler, T. Hillmer, J. Müller and G. Ebbinghaus, Optimization of Zn dopant profiles in a pin-diode/FET by combination of depth profiling techniques: a SIMS, ECV and AES study 50 (1991) 138
- Baumgartner, M. and K. Löhnert, Characterization of si-GaAs wafer quality by room-temperature photoluminescence 50 (1991) 222
- Baurichter, A., M. Deicher, S. Deubler, D. Forkel, J. Meier, H. Wolf, W. Wittmann and ISOLDE Collaboration, Microscopical studies at cadmium impurities in compound semiconductors 50 (1991) 165
- Bausier, E., see Strasser
- Benchiguer, T., E. Christoffel, A. Goltzené, B. Mari, B. Meyer and C. Schwab, Donor-acceptor charge transfers in bulk semi-insulating GaAs as revealed by photo-EPR 50 (1991) 277
- Bender, G., see Herres
- Benyattou, T., see Roura
- Besland, M.P., see Tardy
- Besson, M., see Strasser
- Biglari, B., see Hage-Ali
- Blunt, R., see Pickering
- Bonnet, A., see Morsli
- Bosacchi, A., see Ghezzi
- Bosacchi, A., see Baraldi
- Boudart, B., B. Prévot and C. Schwab, Free-carrier concentration in n-doped InP crystals determined by Raman scattering measurements 50 (1991) 295
- Bowman, Jr., R.C., see Moss
- Brandstättner, M., see Sartorius
- Brec, R., see Morsli

- Bredell, L.J., F.D. Aurret, G. Myburg and W.O. Barnard, Electrical characterization of argon-ion sputtered n-GaAs 50 (1991) 466
- Breivik, L., see Brozel 50 (1991) 475
- Bremond, G., see Hizem 50 (1991) 490
- Bremond, G., see Roura 50 (1991) 496
- Brozel, M.R., see Tüzemen 50 (1991) 395
- Brozel, M.R., L. Breivik, D.J. Stirland, G.M. Williams and A.G. Cullis, Dislocation density, infrared absorption and cathodoluminescence mapping of microstructure associated with dislocation cells in semi-insulating LEC GaAs 50 (1991) 475
- Burkhard, H., see Dinges 50 (1991) 359
- Caillard, D., see Levade 50 (1991) 119
- Callec, R., see L'Haridon 50 (1991) 237
- Carles, R., see Raisin 50 (1991) 434
- Castaldini, A., A. Cavallini, E. Gombia, R. Mosca and L. Tarricone, Evaluation of the diffusion length of minority carriers in bulk GaAs 50 (1991) 485
- Cavallini, A., see Castaldini 50 (1991) 485
- Cerva, H., Transmission electron microscopy of heteroepitaxial layer structures 50 (1991) 19
- Cerva, H., see Schwarz 50 (1991) 456
- Cetronio, A., see Nipoti 50 (1991) 410
- Chen, B.L., M. Eckstein and H.-U. Haberman, Cathodoluminescence investigations of RIE-induced defects in InP 50 (1991) 191
- Chevy, A., see Mari 50 (1991) 415
- Chibani, H., J.P. Stoquert, M. Hage-Ali, J.M. Koebel, M. Abdesselam and P. Siffert, Carbon analysis in CdTe by nuclear activation 50 (1991) 177
- Cho, G.C., see Kütt 50 (1991) 325
- Christoffel, E., see Benchiguer 50 (1991) 277
- Christou, A., see Dimoulas 50 (1991) 353
- Conan, A., see Morsli 50 (1991) 500
- Coquille, R., see L'Haridon 50 (1991) 237
- Couderc, J.J., see Levade 50 (1991) 119
- Couret, A., see Levade 50 (1991) 119
- Crean, G.M., P.A.F. Herbert, I. Little, W.M. Kelly, J.Y. Marzin, A. Izrael and B. Jusserand, Investigation of reactive ion etch-induced damage in InP surfaces using a noncontact photo-thermal radiometric probe 50 (1991) 281
- Cullis, A.G., see Brozel 50 (1991) 475
- D'Anterrosches, C., see Auvray 50 (1991) 109
- De las Heras, C., I.J. Ferrer and C. Sánchez, Comparison of pyrite thin films obtained from Fe and natural pyrite powder 50 (1991) 505
- De Potter, M., see Frigeri 50 (1991) 115
- Deicher, M., see Pfeiffer 50 (1991) 154
- Deicher, M., see Magerle 50 (1991) 159
- Deicher, M., see Baurichter 50 (1991) 165
- Deneuville, A., D.B. Tanner, R.M. Park and P.H. Holloway, Semiconductor electrical properties from the frequency dependence of the dielectric constant: application to n-type ZnSe heteroepitaxial thin films 50 (1991) 285
- Deneuville, A., C.H. Park, P. Ayyub, T. Anderson, P. Lowen, K. Jones and P.H. Holloway, O implantation in ZnSe: lattice distortion by Raman measurement 50 (1991) 308
- Derekis, A., see Dimoulas 50 (1991) 353
- Descouts, B., see Amarger 50 (1991) 462
- Desnica, D.I., B. Šantić and U.V. Desnica, Time-evolution of low-temperature photoconductivity and Hall mobility in semi-insulating GaAs 50 (1991) 269
- Desnica, U., see Magerle 50 (1991) 159
- Desnica, U.V., see Desnica 50 (1991) 269
- Deubler, S., see Baurichter 50 (1991) 165
- Deveaud, B., Subpicosecond luminescence spectroscopy of heterostructures (Extended Abstract) 50 (1991) 63
- Dimoulas, A., A. Derekis, G. Kyriakidis and A. Christou, Alloy disorder effects in III-V ternaries studied by modulation spectroscopy 50 (1991) 353
- Dinges, H.W., B. Kempf, H. Burkhard and R. Göbel, Determination of ion beam etching damage on InP by spectroscopic ellipsometry 50 (1991) 359
- Donegan, J.F., J.P. Doran, R.P. Stanley, J. Hegarty, R.D. Feldman and R.F. Austin, Resonant Rayleigh scattering from excitons in $Cd_xZn_{1-x}Te$: ZnTe quantum wells: measurement of homogeneous linewidths 50 (1991) 321
- Doran, J.P., see Donegan 50 (1991) 321
- Dubois, S., see Strasser 50 (1991) 261
- Dubon-Chevallier, C., see Amarger 50 (1991) 462
- Ebbinghaus, G., see Bauer 50 (1991) 138
- Eckstein, M., see Chen 50 (1991) 191
- Emanuelsson, P., see Meyer 50 (1991) 420
- Endrédi, G., see Horányi 50 (1991) 143
- Fariñas, J.C. and M.F. Barba, Inductively coupled plasma-atomic emission spectrometry (ICP-AES): an analytical technique for the chemical characterization of perovskite ceramic semiconductors 50 (1991) 202
- Favennec, P.N., see L'Haridon 50 (1991) 237

- Feldman, R.D., see Donegan 50 (1991) 321
 Ferrer, I.J., see De las Heras 50 (1991) 505
 Fewster, P.F., Multicrystal X-ray diffraction of heteroepitaxial structures 50 (1991) 9
 Fischer, T., see Schwarz 50 (1991) 456
 Forkel, D., see Pfeiffer 50 (1991) 154
 Forkel, D., see Baurichter 50 (1991) 165
 Fornari, R., N. Tchandjou, P. Gall and J.M. Lussert, A study of structural properties of bulk double-doped InP by laser scattering tomography and photoetching 50 (1991) 207
 Foxon, C.T., Control of MBE, MOMBE and CBE growth using RHEED 50 (1991) 28
 Franchi, S., see Ghezzi 50 (1991) 400
 Franchi, S., see Baraldi 50 (1991) 405
 Frigeri, C., J.L. Weyher and M. De Potter, TEM study of the origin of the surface microroughness in DSL photoetched Si-implanted GaAs wafers 50 (1991) 115
 Gall, P., see Fornari 50 (1991) 207
 Gall, P., see L'Haridon 50 (1991) 237
 Gao, Y., I. Ardelean, D. Renard, B. Rose and Y. Jin, High-depth-resolution SIMS analysis for InGaAs/InP interfaces 50 (1991) 131
 Gao, Y., see Amarger 50 (1991) 462
 Garawal, N.S., see Pickering 50 (1991) 346
 Gauneau, M., see L'Haridon 50 (1991) 237
 Gavand, M., see Hizem 50 (1991) 490
 Geiler, H.D., see Wagner 50 (1991) 373
 Gendry, M., see Tardy 50 (1991) 383
 Ghezzi, C., R. Mosca, A. Bosacchi, S. Franchi and E. Gombia, The influence of the DX center on the capacitance of Schottky barriers in n-type AlGaAs 50 (1991) 400
 Ghezzi, C., see Baraldi 50 (1991) 405
 Giess, J., see Keir 50 (1991) 103
 Glynn, T.J., see O'Connor 50 (1991) 312
 Göbel, H., see Zaus 50 (1991) 92
 Göbel, R., see Dinges 50 (1991) 359
 Godlewski, M., see Heijmink Liesert 50 (1991) 245
 Godlewski, M., see Zakrzewski 50 (1991) 257
 Godlewski, M., see Van Gisbergen 50 (1991) 273
 Goltzené, A., see Benchiguer 50 (1991) 277
 Gombia, E., see Ghezzi 50 (1991) 400
 Gombia, E., see Castaldini 50 (1991) 485
 Gornik, E., see Strasser 50 (1991) 261
 Grattepain, C. and A.M. Huber, Secondary ion mass spectrometry of dopants and impurities in compound semiconductors: depth profiling of homo- and heterostructure 50 (1991) 42
 Gregoire, J., see Hizem 50 (1991) 490
 Gregorkiewicz, T., see Heijmink Liesert 50 (1991) 245
 Gregorkiewicz, T., see Van Gisbergen 50 (1991) 273
 Grimmeiss, H.G. and M. Kleverman, Electrical and optical defect spectroscopy of compound semiconductors 50 (1991) 52
 Grovenor, C.R.M., see Mackenzie 50 (1991) 196
 Guenais, B., see Auvray 50 (1991) 109
 Guillot, G., see Hizem 50 (1991) 490
 Guillot, G., see Roura 50 (1991) 496
 Gumienny, Z., see Jezierski 50 (1991) 341
 Gusinsky, G.M., see Kudoyarova 50 (1991) 173
 Gustafsson, A., S. Nilsson and L. Samuelson, Intensity variations in the near-band-edge recombination of GaP epitaxial layers, grown on (111) and (001) oriented substrates, as observed by cathodoluminescence imaging 50 (1991) 186
 Habermeier, H.-U., see Chen 50 (1991) 191
 Hage-Ali, M., see Chibani 50 (1991) 177
 Hage-Ali, M., B. Yaacoub, S. Mergui, M. Samimi, B. Biglari and P. Siffert, Microscopic defect level characterization of semi-insulating compound semiconductors by TSC and PICTS. Application to the effect of hydrogen in CdTe 50 (1991) 377
 Hanesch, P., see Schwarz 50 (1991) 456
 Hegarty, J., see Donegan 50 (1991) 321
 Heijmink Liesert, B.J., M. Godlewski, T. Gregorkiewicz and C.A.J. Ammerlaan, Neutron transmutation doping of GaP: optical studies 50 (1991) 245
 Henry, M.O., see O'Connor 50 (1991) 312
 Herbert, P.A.F., see Crean 50 (1991) 281
 Hergert, W., see Schreiber 50 (1991) 181
 Herres, N., G. Bender and G. Neumann, Assessment of mismatched epitaxial layers by X-ray rocking curve measurements and simulations 50 (1991) 97
 Herzog, H.-J., see Holländer 50 (1991) 450
 Hettwer, H.-G., W. Lerch, B. Lentfort, N.A. Stolwijk and H. Mehrer, Combined application of spreading-resistance and electron-microprobe depth profiling on GaAs:Zn and Si:P 50 (1991) 470
 Hildebrandt, S., see Schreiber 50 (1991) 181
 Hillmer, T., see Bauer 50 (1991) 138
 Hizem, N., G. Bremond, L. Mayet, M. Gavand, J. Gregoire, G. Guillot and W. Ulrici, Identification of the double and single acceptor state of isolated Ni_{Ga} in GaAs 50 (1991) 490
 Hofmann, D., see Mosel 50 (1991) 364
 Hofsäss, H., see Jahn 50 (1991) 169
 Hogg, J.H.C., D. Shaw and D.M. Staudte, Modelling interdiffusion in epitaxial multilayer structures using X-ray simulation techniques 50 (1991) 87

- Hogg, J.H.C., see Ashenford 50 (1991) 440
- Holländer, B., S. Mantl, B. Stritzker, F. Schäffler, H.-J. Herzog and E. Kasper, Strain and defect densities in Si/Si_{1-x}Ge_x heterostructures investigated by ion scattering and X-ray diffraction 50 (1991) 450
- Holloway, P.H., see Deneuveille 50 (1991) 285
- Holloway, P.H., see Deneuveille 50 (1991) 308
- Horányi, T.S., P. Tüttö and G. Endrédi, Improved method for depth profiling of multilayer structures 50 (1991) 143
- Houlton, M.R., see Lee 50 (1991) 428
- Huber, A.M., see Grattepain 50 (1991) 42
- Hughes, G., see Roberts 50 (1991) 424
- Hughes, G.J., see O'Connor 50 (1991) 312
- Ipatova, I.P., see Bairamov 50 (1991) 300
- Irmer, G., see Bairamov 50 (1991) 300
- ISOLDE Collaboration, see Baurichter 50 (1991) 165
- ISOLDE Collaboration, see Jahn 50 (1991) 169
- Izrael, A., see Crean 50 (1991) 281
- Jahn, S.G., H. Hofsäss, U. Wahl, S. Winter, E. Recknagel and ISOLDE Collaboration, Structural defect recovery in GaP after heavy ion implantation 50 (1991) 169
- Jahne, E., see Bairamov 50 (1991) 300
- Jantz, W., see Wang 50 (1991) 228
- Jantz, W., R. Stibal, J. Windscheif and J. Wagner, Variation of material parameters along the growth direction of liquid encapsulated Czochralski grown GaAs ingots 50 (1991) 480
- Jezierski, K., Z. Gumieny and J. Misiewicz, Reflectometry-aided surface layer investigation 50 (1991) 341
- Jin, Y., see Gao 50 (1991) 131
- Jobic, S., see Morsli 50 (1991) 500
- Jones, K., see Deneuveille 50 (1991) 308
- Jusserand, B., see Crean 50 (1991) 281
- Jusserand, B. and F. Mollot, Confined optical vibrations: a new probe for alloy disorder 50 (1991) 317
- Kaliński, Z., see Tatarkiewicz 50 (1991) 249
- Kalish, R., see Pfeiffer 50 (1991) 154
- Kasper, E., see Holländer 50 (1991) 450
- Kaufel, G., see Zappe 50 (1991) 290
- Keir, A.M., S.J. Barnett, J. Giess, T.D. Walsh and M.G. Astles, A combination of high-resolution X-ray diffractometry and diffraction imaging techniques applied to the study of MOVPE-grown Cd_xHg_{1-x}Te/CdTe on GaAs 50 (1991) 103
- Keller, R., see Pfeiffer 50 (1991) 154
- Keller, R., see Magerle 50 (1991) 159
- Kelly, W.M., see Crean 50 (1991) 281
- Kempf, B., see Dinges 50 (1991) 359
- Kleverman, M., see Grimmeiss 50 (1991) 52
- Knudsen, J.F., see Moss 50 (1991) 337
- Koebel, J.M., see Chibani 50 (1991) 177
- Kolodzey, J., see Schwarz 50 (1991) 456
- Kozanecki, A., see Tatarkiewicz 50 (1991) 249
- Kudoyarova, V.Kh., G.M. Gusinsky, L.A. Rassadin and I.V. Kudryavtsev, Hydrogen depth profile measurement in a-Si_{1-x}C_xH films by elastic recoil detection 50 (1991) 173
- Kudryavtsev, I.V., see Kudoyarova 50 (1991) 173
- Kurz, H., see Kütt 50 (1991) 325
- Kütt, W., G.C. Cho, M. Strahnen and H. Kurz, Electro-optic sampling of surface space-charge fields on III-V compounds 50 (1991) 325
- Kyriakidis, G., see Dimoulas 50 (1991) 353
- Lacquet, B.M., see Swart 50 (1991) 330
- Lamberti, C., see Antolini 50 (1991) 212
- Lancefield, D., see Pickering 50 (1991) 346
- Landa, G., see Raisin 50 (1991) 434
- Lanzieri, C., see Nipoti 50 (1991) 410
- Lassabater, L., see Raisin 50 (1991) 434
- Le Guillou, Y., see L'Haridon 50 (1991) 237
- Lee, D., S.J. Barnett, A.D. Pitt, M.R. Houlton and G.W. Smith, Characterization of alloy composition in Ga_{1-x}Al_xAs/GaAs structures: comparison of photovoltage, X-ray, SIMS and RHEED techniques 50 (1991) 428
- Leitch, A.W.R., Th. Prescha and M. Stutzmann, Hydrogen passivation and reactivation of shallow Zn acceptors in GaAs 50 (1991) 390
- Lentfort, B., see Hettwer 50 (1991) 470
- Lerch, W., see Hettwer 50 (1991) 470
- Levade, C., J.J. Couderc, G. Vander-schaeve, D. Caillard and A. Couret, TEM in-situ observation of recombination-enhanced mobility of dislocations in II-VI compounds 50 (1991) 119
- L'Haridon, H., P.N. Favennec, R. Coquille, M. Salvi, M. Gauneau, Y. Le Guillou, R. Callec and P. Gall, Spatial investigation of an iron-doped indium phosphide ingot 50 (1991) 237
- Liddle, J.A., see Mackenzie 50 (1991) 196
- Little, I., see Crean 50 (1991) 281
- Löhnert, K., see Baumgartner 50 (1991) 222
- Louis, P., see Tardy 50 (1991) 383
- Lowen, P., see Deneuveille 50 (1991) 308

- Lunn, B., see Ashenford 50 (1991) 440
 Lussert, J.M., see Fornari 50 (1991) 207
- Mackenzie, R.A.D., J.A. Little and C.R.M. Grovenor, Ultrahigh resolution characterisation of compound semiconductors using pulsed laser atom probe techniques 50 (1991) 196
 Magerle, R., see Pfeiffer 50 (1991) 154
 Magerle, R., M. Deicher, U. Desnica, R. Keller, W. Pfeiffer, F. Pleiter, H. Skudlik and Th. Wichert, Defects in CdS:In detected by perturbed angular correlation spectroscopy (PAC) 50 (1991) 159
 Makita, Y., see Ohnishi 50 (1991) 233
 Mantl, S., see Holländer 50 (1991) 450
 Mari, B., see Benchiguer 50 (1991) 277
 Mari, B., A. Segura and A. Chevy, Electrical properties of neutron-transmutation-doped InSe 50 (1991) 415
 Marzin, J.Y., see Crean 50 (1991) 281
 Massies, J., see Auvray 50 (1991) 109
 Matsui, J., Study of strain variation in LEC-grown GaAs bulk crystals by synchrotron radiation X-ray topography 50 (1991) 1
 Matsumori, T., see Ohnishi 50 (1991) 233
 Mayet, L., see Hizem 50 (1991) 490
 McDonagh, C.J., see O'Connor 50 (1991) 312
 McGovern, I.T., Soft X-ray photoelectron spectroscopy of compound semiconductor surfaces and interfaces 50 (1991) 34
 Mehrer, H., see Hettwer 50 (1991) 470
 Meier, J., see Baurichter 50 (1991) 165
 Mendik, M., M. Ospelt, H. von Känel and P. Wachter, Determination of elastic properties of Si/Ge superlattices and $\text{Si}_{1-x}\text{Ge}_x$ films from surface acoustic modes by Brillouin scattering 50 (1991) 303
 Mergui, S., see Hage-Ali 50 (1991) 377
 Meyer, B., see Benchiguer 50 (1991) 277
 Meyer, B., P. Omling and P. Emanuelsson, Landau oscillations in single quantum wells observed by microwave detection 50 (1991) 420
 Meyerheim, H.L., see Schwarz 50 (1991) 456
 Misiewicz, J., see Jezierski 50 (1991) 341
 Missous, M., see Rimmer 50 (1991) 149
 Mollot, F., see Jusserand 50 (1991) 317
 Monecke, J., see Bairamov 50 (1991) 300
 Monteiro, T. and E. Pereira, Complex formation in Mn-doped GaP samples 50 (1991) 253
 Morante, J.R., see Roura 50 (1991) 496
 Morgan, G.P., see O'Connor 50 (1991) 312
 Moriya, N., see Pfeiffer 50 (1991) 154
 Morsli, M., A. Bonnet, Y. Tregouet, A. Conan, S. Jobic and R. Brec, Electronic properties and band structure of IrSe_2 50 (1991) 500
 Mosca, R., see Ghezzi 50 (1991) 400
 Mosca, R., see Castaldini 50 (1991) 485
 Mosel, F., A. Seidl, D. Hofmann and G. Müller, Infrared absorption of n- and p-type Fe-doped InP and mapping of the Fe distribution 50 (1991) 364
 Moss, S.C., J.F. Knudsen, R.C. Bowman, Jr., P.M. Adams and D.D. Smith, Picosecond transient photoreflectance measurements of ion-implanted GaAs 50 (1991) 337
 Müller, G., see Mosel 50 (1991) 364
 Müller, J., see Bauer 50 (1991) 138
 Muschik, T., see Schwarz 50 (1991) 456
 Myburg, G., see Bredell 50 (1991) 466
- Nesladek, M., see Usala 50 (1991) 265
 Neumann, G., see Herres 50 (1991) 97
 Nilsson, S., see Gustafsson 50 (1991) 186
 Nipoti, R., D. Pocci, A. Cetronio and C. Lanzieri, Carrier and mobility profile measurements in n-type ion-implanted GaAs by the differential sheet resistivity and Hall effect technique 50 (1991) 410
- O'Connor, G.M., C.J. McDonagh, F.G. Anderson, T.J. Glynn, G.P. Morgan, G.J. Hughes, L. Roberts and M.O. Henry, Raman characterization of passivated GaAs surfaces 50 (1991) 312
 Ohnishi, N., Y. Makita, A. Yamada, H. Asakura and T. Matsumori, Effect of substrate orientation on the defect-induced bound exciton emissions in GaAs grown by molecular beam epitaxy 50 (1991) 233
 Öktü, Ö., see Usala 50 (1991) 265
 Omling, P., see Meyer 50 (1991) 420
 Ospelt, M., see Mendik 50 (1991) 303
 Ossart, P. and E.V.K. Rao, Investigation of surface and sub-surface defects on polished InP substrates using Auger electron spectroscopy coupled to argon ion sputtering 50 (1991) 125
- Papadopoulos, A.C., see Amarger 50 (1991) 462
 Paprocki, K., see Tatarkiewicz 50 (1991) 249
 Parisini, A., see Baraldi 50 (1991) 405
 Park, C.H., see Deneuve 50 (1991) 308
 Park, R.M., see Deneuve 50 (1991) 285
 Peaker, A.R., see Rimmer 50 (1991) 149
 Pereira, E., see Monteiro 50 (1991) 253
 Perrossier, J.L., see Tardy 50 (1991) 383

- Pfeiffer, W., M. Deicher, R. Keller, R. Magerle, P. Pross, H. Skudlik, Th. Wichert, H. Wolf, D. Forkel, N. Moriya and R. Kalish, Characterization of Cd implanted and annealed GaAs and InP by perturbed angular correlation (PAC) spectroscopy 50 (1991) 154
- Pfeiffer, W., see Magerle 50 (1991) 159
- Pickering, C., N.S. Garawal, D. Lancefield, J.P. Piel and R. Blunt, Non-destructive characterisation of (Ga,In,Al,As,P)-based ternary multilayer structures using spectroscopic ellipsometry 50 (1991) 346
- Piel, J.P., see Pickering 50 (1991) 346
- Pitt, A.D., see Lee 50 (1991) 428
- Pleiter, F., see Magerle 50 (1991) 159
- Pocci, D., see Nipoti 50 (1991) 410
- Post, G., see Tardy 50 (1991) 383
- Poudoulec, A., see Auvray 50 (1991) 109
- Prescha, Th., see Leitch 50 (1991) 390
- Prévot, B., see Boudart 50 (1991) 295
- Pross, P., see Pfeiffer 50 (1991) 154
- Raisin, C., A. Rocher, G. Landa, R. Carles and L. Lassabatre, GaSb/GaAs heteroepitaxy characterized as a stress-free system 50 (1991) 434
- Rao, E.V.K., see Ossart 50 (1991) 125
- Rassadin, L.A., see Kudoyarova 50 (1991) 173
- Recknagel, E., see Jahn 50 (1991) 169
- Regreny, A., see Auvray 50 (1991) 109
- Reithmaier, J.-P., see Zaus 50 (1991) 92
- Renard, D., see Gao 50 (1991) 131
- Riechert, H., see Strasser 50 (1991) 261
- Rimmer, J.S., M. Misous and A.R. Peaker, A new, fast method for the computer simulation of CV profiles in multilayer structures 50 (1991) 149
- Roberts, L., see O'Connor 50 (1991) 312
- Roberts, L. and G. Hughes, An investigation of metal/GaAs(100) interfaces by deep level transient spectroscopy 50 (1991) 424
- Rocher, A., see Raisin 50 (1991) 434
- Rose, B., see Gao 50 (1991) 131
- Roura, P., J.R. Morante, G. Bremond, T. Benyattou, G. Guillot and W. Ulrici, Complete identification of the Ti-related levels in GaP 50 (1991) 496
- Salvi, M., see L'Haridon 50 (1991) 237
- Samimi, M., see Hage-Ali 50 (1991) 377
- Samuelson, L., see Gustafsson 50 (1991) 186
- Sánchez, C., see De las Heras 50 (1991) 505
- Santić, B., see Desnica 50 (1991) 269
- Santinelli, C., see Tardy 50 (1991) 383
- Sartorius, B., M. Brandstättner and H. Venghaus, Two-wavelength transmission: a rapid and precise method for measuring the light absorption in semiconductors 50 (1991) 369
- Schäffler, F., see Holländer 50 (1991) 450
- Scherzer, B.M.U., see Schwarz 50 (1991) 456
- Schreiber, J., W. Hergert and S. Hildebrandt, Combined application of SEM-CL and SEM-EBIC for the investigation of compound semiconductors 50 (1991) 181
- Schuster, M., see Zaus 50 (1991) 92
- Schwab, C., see Benchiguer 50 (1991) 277
- Schwab, C., see Boudart 50 (1991) 295
- Schwarz, R., T. Fischer, P. Hanesch, T. Muschik, J. Kolodzey, H. Cerva, H.L. Meyerheim and B.M.U. Scherzer, Limitations of interface sharpness in a-Si:H/a-SiC:H multilayers 50 (1991) 456
- Scott, C.G., see Ashenford 50 (1991) 440
- Segura, A., see Mari 50 (1991) 415
- Seidl, A., see Mosel 50 (1991) 364
- Shaw, D., see Hogg 50 (1991) 87
- Siffert, P., see Chibani 50 (1991) 177
- Siffert, P., see Hage-Ali 50 (1991) 377
- Skudlik, H., see Pfeiffer 50 (1991) 154
- Skudlik, H., see Magerle 50 (1991) 159
- Smith, D.D., see Moss 50 (1991) 337
- Smith, G.W., see Lee 50 (1991) 428
- Stanley, R.P., see Donegan 50 (1991) 321
- Staudte, D.M., see Hogg 50 (1991) 87
- Stibal, R., see Jantz 50 (1991) 480
- Stirland, D.J., see Brozel 50 (1991) 475
- Stolwijk, N.A., see Hettwer 50 (1991) 470
- Stoquert, J.P., see Chibani 50 (1991) 177
- Stradling, R.A., Far-infrared spectroscopy of impurities in semiconductors 50 (1991) 65
- Strahnen, M., see Kütt 50 (1991) 325
- Strasser, G., S. Dubois, M. Besson, E. Gornik, G. Weimann, E. Bauser and H. Riechert, Analysis of impurity distribution in n-GaAs layers by photoconductivity and cyclotron resonance measurements 50 (1991) 261
- Stritzker, B., see Holländer 50 (1991) 450
- Stutzmann, M., see Leitch 50 (1991) 390
- Swart, P.L., B.M. Lacquet and R. Thavar, Physical characterization of OMVPE-grown Al_xGa_{1-x}As multi-layer films by means of non-destructive optical reflectometry 50 (1991) 330
- Tanner, D.B., see Deneuille 50 (1991) 285
- Tardy, J., I. Thomas, P. Viktorovitch, M. Gendry, J.L. Perrossier, C. Santinelli, M.P. Besland, P. Louis and G. Post,

- Long-term stability of InP MIS devices 50 (1991) 383
- Tarricone, L., see Castaldini 50 (1991) 485
- Tatarkiewicz, J., A. Kozanecki, Z. Kaliński and K. Paprocki, Photoluminescence study of proton-implanted $\text{InP}_{1-x}\text{As}_x\text{:Yb}$ 50 (1991) 249
- Tchandjou, N., see Fornari 50 (1991) 207
- Thavar, R., see Swart 50 (1991) 330
- Thomas, I., see Tardy 50 (1991) 383
- Toporov, V.V., see Bairamov 50 (1991) 300
- Tregouet, Y., see Morsli 50 (1991) 500
- Treichler, R., see Bauer 50 (1991) 138
- Tüttö, P., see Horányi 50 (1991) 143
- Tüzemen, S. and M.R. Brozel, An investigation of photo-quenching properties of LEC GaAs by using optical and electrical techniques 50 (1991) 395
- Ulrici, W., see Hizem 50 (1991) 490
- Ulrici, W., see Roura 50 (1991) 496
- Usala, S., G.J. Adriaenssens, Ö. Öktü and M. Nesladek, Post-transit-time analysis of time-of-flight photocurrents 50 (1991) 265
- Van Gisbergen, S.J.C.H.M., M. Godlewski, T. Gregorkiewicz and C.A.J. Ammerlaan, Interstitial Mn as a new donor in GaP and GaAs: an EPR study 50 (1991) 273
- Vanderschaeve, G., see Levade 50 (1991) 119
- Venghaus, H., see Sartorius 50 (1991) 369
- Viktorovitch, P., see Tardy 50 (1991) 383
- Voitenko, V.A., see Bairamov 50 (1991) 300
- Von Känel, H., see Mendik 50 (1991) 303
- Wachter, P., see Mendik 50 (1991) 303
- Wagner, J., Raman spectroscopy for impurity characterization in III-V semiconductors 50 (1991) 79
- Wagner, J., see Jantz 50 (1991) 480
- Wagner, M., N. Winkler and H.D. Geiler, Single-beam thermowave analysis of semiconductors 50 (1991) 373
- Wahl, U., see Jahn 50 (1991) 169
- Walsh, T.D., see Keir 50 (1991) 103
- Wang, Z.M., J. Windscheif, D.J. As and W. Jantz, Ambient and low temperature photoluminescence topography of GaAs substrates, epitaxial and implanted layers 50 (1991) 228
- Weimann, G., see Strasser 50 (1991) 261
- Westwood, D.I., see Woolf 50 (1991) 445
- Weyher, J.L., see Frigeri 50 (1991) 115
- Wichert, Th., see Pfeiffer 50 (1991) 154
- Wichert, Th., see Magerle 50 (1991) 159
- Williams, G.M., see Brozel 50 (1991) 475
- Williams, R.H., see Woolf 50 (1991) 445
- Windscheif, J., see Wang 50 (1991) 228
- Windscheif, J., see Jantz 50 (1991) 480
- Winkler, N., see Wagner 50 (1991) 373
- Winter, S., see Jahn 50 (1991) 169
- Witthuhn, W., see Baurichter 50 (1991) 165
- Wolf, H., see Pfeiffer 50 (1991) 154
- Wolf, H., see Baurichter 50 (1991) 165
- Woolf, D.A., D.I. Westwood, M.A. Anderson and R.H. Williams, The molecular beam epitaxial growth of GaAs(111)/Si(111): a variable growth temperature study 50 (1991) 445
- Yaacoub, B., see Hage-Ali 50 (1991) 377
- Yamada, A., see Ohnishi 50 (1991) 233
- Zakrzewski, A. and M. Godlewski, Three-center Auger effect and the quantum yield of the luminescence of ZnS-based phosphors 50 (1991) 257
- Zappe, H.P. and G. Kaufel, Reactive-ion-etch damage in GaAs processing evaluated by a microwave absorption technique 50 (1991) 290
- Zaus, R., M. Schuster, H. Göbel and J.-P. Reithmaier, Characterization of (In, Ga)As/GaAs strained-layer multiple quantum wells with high-resolution X-ray diffraction and computer simulations 50 (1991) 92

Subject index

Aluminium

- P.L. Swart, B.M. Lacquet and R. Thavar,
Physical characterization of OMVPE-
grown $\text{Al}_x\text{Ga}_{1-x}\text{As}$ multi-layer films
by means of non-destructive optical
reflectometry 50 (1991) 330
- K. Jezierski, Z. Gumieny and J. Mis-
iewicz, Reflectometry-aided surface
layer investigation 50 (1991) 341

Amorphous materials

- V.Kh. Kudoyarova, G.M. Gusinsky, L.A.
Rassadin and I.V. Kudryavtsev, Hy-
drogen depth profile measurement in
 $\text{a-Si}_{1-x}\text{C}_x\text{:H}$ films by elastic recoil de-
tection 50 (1991) 173
- S. Usala, G.J. Adriaenssens, Ö. Öktü and
M. Nesladek, Post-transit-time analy-
sis of time-of-flight photocurrents 50 (1991) 265
- R. Schwarz, T. Fischer, P. Hanesch, T.
Muschik, J. Kolodzey, H. Cerva, H.L.
Meyerheim and B.M.U. Scherzer,
Limitations of interface sharpness in
 a-Si:H/a-SiC:H multilayers 50 (1991) 456

Annealing

- W. Pfeiffer, M. Deicher, R. Keller, R.
Magerle, P. Pross, H. Skudlik, Th.
Wichert, H. Wolf, D. Forkel, N.
Moriya and R. Kalish, Characteriza-
tion of Cd implanted and annealed
GaAs and InP by perturbed angular
correlation (PAC) spectroscopy 50 (1991) 154
- S.G. Jahn, H. Hofsäss, U. Wahl, S. Winter,
E. Recknagel and ISOLDE Collabora-
tion, Structural defect recovery in GaP
after heavy ion implantation 50 (1991) 169
- M. Baumgartner and K. Löhnert, Char-
acterization of si-GaAs wafer quality
by room-temperature photolumines-
cence 50 (1991) 222
- Z.M. Wang, J. Windscheif, D.J. As and
W. Jantz, Ambient and low tempera-
ture photoluminescence topography of

- GaAs substrates, epitaxial and im-
planted layers 50 (1991) 228
- H. L'Haridon, P.N. Favenne, R. Co-
quille, M. Salvi, M. Gauneau, Y. Le
Guillou, R. Callec and P. Gall, Spatial
investigation of an iron-doped indium
phosphide ingot 50 (1991) 237
- J. Tatarkiewicz, A. Kozanecki, Z. Kaliń-
ski and K. Paprocki, Photolumines-
cence study of proton-implanted
 $\text{InP}_{1-x}\text{As}_x\text{:Yb}$ 50 (1991) 249
- A. Deneuve, C.H. Park, P. Ayyub, T.
Anderson, P. Lowen, K. Jones and
P.H. Holloway, O implantation in
ZnSe: lattice distortion by Raman
measurement 50 (1991) 308
- M. Wagner, N. Winkler and H.D. Geiler,
Single-beam thermowave analysis of
semiconductors 50 (1991) 373
- V. Amarger, C. Dubon-Chevallier, A.C.
Papadopoulos, B. Descouts and Y. Gao,
Correlated use of characterization
techniques to optimize the Mg implan-
tation annealing for self-aligned HBT's
50 (1991) 462
- L.J. Bredell, F.D. Aret, G. Myburg and
W.O. Barnard, Electrical characteriza-
tion of argon-ion sputtered n-GaAs 50 (1991) 466

Auger electron spectroscopy

- P. Ossart and E.V.K. Rao, Investigation
of surface and sub-surface defects on
polished InP substrates using Auger
electron spectroscopy coupled to argon
ion sputtering 50 (1991) 125
- J.G. Bauer, R. Treichler, T. Hillmer, J.
Müller and G. Ebbinghaus, Optimiza-
tion of Zn dopant profiles in a pin-di-
ode/FET by combination of depth
profiling techniques: a SIMS, ECV
and AES study 50 (1991) 138

Band structure

- M. Morsli, A. Bonnet, Y. Tregouet, A.
Conan, S. Jobic and R. Brec, Elec-
tronic properties and band structure
of IrSe_2 50 (1991) 500

Cadmium

- W. Pfeiffer, M. Deicher, R. Keller, R. Magerle, P. Pross, H. Skudlik, Th. Wichert, H. Wolf, D. Forkel, N. Moriya and R. Kalish, Characterization of Cd implanted and annealed GaAs and InP by perturbed angular correlation (PAC) spectroscopy 50 (1991) 154
- A. Baurichter, M. Deicher, S. Deubler, D. Forkel, J. Meier, H. Wolf, W. Witt-huhn and ISOLDE Collaboration, Microscopical studies at cadmium impurities in compound semiconductors 50 (1991) 165
- S.G. Jahn, H. Hofsäuss, U. Wahl, S. Winter, E. Recknagel and ISOLDE Collaboration, Structural defect recovery in GaP after heavy ion implantation 50 (1991) 169

Cadmium sulphide

- I.T. McGovern, Soft X-ray photoelectron spectroscopy of compound semiconductor surfaces and interfaces 50 (1991) 34
- R. Magerle, M. Deicher, U. Desnica, R. Keller, W. Pfeiffer, F. Pleiter, H. Skudlik and Th. Wichert, Defects in CdS:In detected by perturbed angular correlation spectroscopy (PAC) 50 (1991) 159
- R. Fornari, N. Tchandjou, P. Gall and J.M. Lussert, A study of structural properties of bulk double-doped InP by laser scattering tomography and photoetching 50 (1991) 207

Cadmium telluride

- J.H.C. Hogg, D. Shaw and D.M. Staudte, Modelling interdiffusion in epitaxial multilayer structures using X-ray simulation techniques 50 (1991) 87
- A.M. Keir, S.J. Barnett, J. Giess, T.D. Walsh and M.G. Astles, A combination of high-resolution X-ray diffractometry and diffraction imaging techniques applied to the study of MOVPE-grown $\text{Cd}_x\text{Hg}_{1-x}\text{Te}$ /CdTe on GaAs 50 (1991) 103
- C. Levade, J.J. Couderc, G. Vanderschaeve, D. Caillard and A. Couret, TEM in-situ observation of recombination-enhanced mobility of dislocations in II-VI compounds 50 (1991) 119
- H. Chibani, J.P. Stoquert, M. Hage-Ali, J.M. Koebel, M. Abdesselam and P.

Siffert, Carbon analysis in CdTe by nuclear activation 50 (1991) 177

- M. Hage-Ali, B. Yaacoub, S. Mergui, M. Samimi, B. Biglari and P. Siffert, Microscopic defect level characterization of semi-insulating compound semiconductors by TSC and PICTS. Application to the effect of hydrogen in CdTe 50 (1991) 377
- D. Ashenford, J.H.C. Hogg, B. Lunn and C.G. Scott, The relationship between electrical and structural characteristics of CdTe and CdMnTe layers grown on InSb 50 (1991) 440

Carbon

- H. Chibani, J.P. Stoquert, M. Hage-Ali, J.M. Koebel, M. Abdesselam and P. Siffert, Carbon analysis in CdTe by nuclear activation 50 (1991) 177

Ceramics

- J.C. Fariñas and M.F. Barba, Inductively coupled plasma-atomic emission spectrometry (ICP-AES): an analytical technique for the chemical characterization of perovskite ceramic semiconductors 50 (1991) 202

Chalcogenides

- A. Deneuve, D.B. Tanner, R.M. Park and P.H. Holloway, Semiconductor electrical properties from the frequency dependence of the dielectric constant: application to n-type ZnSe heteroepitaxial thin films 50 (1991) 285
- A. Deneuve, C.H. Park, P. Ayyub, T. Anderson, P. Lowen, K. Jones and P.H. Holloway, O implantation in ZnSe: lattice distortion by Raman measurement 50 (1991) 308
- J.F. Donegan, J.P. Doran, R.P. Stanley, J. Hegarty, R.D. Feldman and R.F. Austin, Resonant Rayleigh scattering from excitons in $\text{Cd}_x\text{Zn}_{1-x}\text{Te}$:ZnTe quantum wells: measurement of homogeneous linewidths 50 (1991) 321
- B. Mari, A. Segura and A. Chevy, Electrical properties of neutron-transmutation-doped InSe 50 (1991) 415
- M. Morsli, A. Bonnet, Y. Tregouet, A. Conan, S. Jobic and R. Brec, Elec-

- tronic properties and band structure of IrSe_2 50 (1991) 500
- Chemical vapour deposition*
- C.T. Foxon, Control of MBE, MOMBE and CBE growth using RHEED 50 (1991) 28
- Cyclotron resonance studies*
- G. Strasser, S. Dubois, M. Besson, E. Gornik, G. Weimann, E. Bauser and H. Riechert, Analysis of impurity distribution in n-GaAs layers by photoconductivity and cyclotron resonance measurements 50 (1991) 261
- Diffusion*
- J.H.C. Hogg, D. Shaw and D.M. Staudte, Modelling interdiffusion in epitaxial multilayer structures using X-ray simulation techniques 50 (1991) 87
- J.G. Bauer, R. Treichler, T. Hillmer, J. Müller and G. Ebbinghaus, Optimization of Zn dopant profiles in a pin-diode/FET by combination of depth profiling techniques: a SIMS, ECV and AES study 50 (1991) 138
- R. Magerle, M. Deicher, U. Desnica, R. Keller, W. Pfeiffer, F. Pleiter, H. Skudlik and Th. Wichert, Defects in CdS:In detected by perturbed angular correlation spectroscopy (PAC) 50 (1991) 159
- S.J.C.H.M. van Gisbergen, M. Godlewski, T. Gregorkiewicz and C.A.J. Ammerlaan, Interstitial Mn as a new donor in GaP and GaAs: an EPR study 50 (1991) 273
- H.-G. Hettwer, W. Lerch, B. Lentfort, N.A. Stolwijk and H. Mehrer, Combined application of spreading-resistance and electron-microprobe depth profiling on GaAs:Zn and Si:P 50 (1991) 470
- Doping effects*
- J. Matsui, Study of strain variation in LEC-grown GaAs bulk crystals by synchrotron radiation X-ray topography 50 (1991) 1
- C. Grattapain and A.M. Huber, Secondary ion mass spectrometry of dopants and impurities in compound semiconductors: depth profiling of homo- and heterostructure 50 (1991) 42
- H. L'Haridon, P.N. Favenec, R. Coquille, M. Salvi, M. Gauneau, Y. Le Guillou, R. Callec and P. Gall, Spatial investigation of an iron-doped indium phosphide ingot 50 (1991) 237
- T. Monteiro and E. Pereira, Complex formation in Mn-doped GaP samples 50 (1991) 253
- A. Deneuve, D.B. Tanner, R.M. Park and P.H. Holloway, Semiconductor electrical properties from the frequency dependence of the dielectric constant: application to n-type ZnSe heteroepitaxial thin films 50 (1991) 285
- B. Boudart, B. Prévot and C. Schwab, Free-carrier concentration in n-doped InP crystals determined by Raman scattering measurements 50 (1991) 295
- F. Mosel, A. Seidl, D. Hofmann and G. Müller, Infrared absorption of n- and p-type Fe-doped InP and mapping of the Fe distribution 50 (1991) 364
- B. Sartorius, M. Brandstättner and H. Venghaus, Two-wavelength transmission: a rapid and precise method for measuring the light absorption in semiconductors 50 (1991) 369
- R. Nipoti, D. Pucci, A. Cetronio and C. Lanzieri, Carrier and mobility profile measurements in n-type ion-implanted GaAs by the differential sheet resistivity and Hall effect technique 50 (1991) 410
- B. Mari, A. Segura and A. Chevy, Electrical properties of neutron-transmutation-doped InSe 50 (1991) 415
- D. Ashenford, J.H.C. Hogg, B. Lunn and C.G. Scott, The relationship between electrical and structural characteristics of CdTe and CdMnTe layers grown on InSb 50 (1991) 440
- A. Castaldini, A. Cavallini, E. Gombia, R. Mosca and L. Tarricone, Evaluation of the diffusion length of minority carriers in bulk GaAs 50 (1991) 485
- N. Hizem, G. Bremond, L. Mayet, M. Gavand, J. Gregoire, G. Guillot and W. Ulrici, Identification of the double and single acceptor state of isolated Ni_{Ga} in GaAs 50 (1991) 490
- P. Roura, J.R. Morante, G. Bremond, T. Benyattou, G. Guillot and W. Ulrici, Complete identification of the Ti-related levels in GaP 50 (1991) 496
- Electrical properties*
- H.G. Grimmeiss and M. Kleverman, Electrical and optical defect spec-

- troscopy of compound semiconductors 50 (1991) 52
- T.S. Horányi, P. Tüttö and G. Endrédi, Improved method for depth profiling of multilayer structures 50 (1991) 143
- J.S. Rimmer, M. Missous and A.R. Peaker, A new, fast method for the computer simulation of *CV* profiles in multilayer structures 50 (1991) 149
- J. Schreiber, W. Hergert and S. Hildebrandt, Combined application of SEM-CL and SEM-EBIC for the investigation of compound semiconductors 50 (1991) 181
- Z.M. Wang, J. Windscheif, D.J. As and W. Jantz, Ambient and low temperature photoluminescence topography of GaAs substrates, epitaxial and implanted layers 50 (1991) 228
- H. L'Haridon, P.N. Favennec, R. Coquille, M. Salvi, M. Gauneau, Y. Le Guillou, R. Callec and P. Gall, Spatial investigation of an iron-doped indium phosphide ingot 50 (1991) 237
- A. Deneuville, D.B. Tanner, R.M. Park and P.H. Holloway, Semiconductor electrical properties from the frequency dependence of the dielectric constant: application to n-type ZnSe heteroepitaxial thin films 50 (1991) 285
- H.P. Zappe and G. Kaufel, Reactive-ion-etch damage in GaAs processing evaluated by a microwave absorption technique 50 (1991) 290
- W. Kütt, G.C. Cho, M. Strahnen and H. Kurz, Electro-optic sampling of surface space-charge fields on III-V compounds 50 (1991) 325
- M. Hage-Ali, B. Yaacoub, S. Mergui, M. Samimi, B. Biglari and P. Siffert, Microscopic defect level characterization of semi-insulating compound semiconductors by TSC and PICTS. Application to the effect of hydrogen in CdTe 50 (1991) 377
- J. Tardy, I. Thomas, P. Viktorovitch, M. Gendry, J.L. Perrossier, C. Santinelli, M.P. Besland, P. Louis and G. Post, Long-term stability of InP MIS devices 50 (1991) 383
- A.W.R. Leitch, Th. Prescha and M. Stutzmann, Hydrogen passivation and reactivation of shallow Zn acceptors in GaAs 50 (1991) 390
- S. Tüzemen and M.R. Brozel, An investigation of photo-quenching properties of LEC GaAs by using optical and electrical techniques 50 (1991) 395
- C. Ghezzi, R. Mosca, A. Bosacchi, S. Franchi and E. Gombia, The influence of the DX center on the capacitance of Schottky barriers in n-type AlGaAs 50 (1991) 400
- R. Nipoti, D. Pucci, A. Cetronio and C. Lanzieri, Carrier and mobility profile measurements in n-type ion-implanted GaAs by the differential sheet resistivity and Hall effect technique 50 (1991) 410
- B. Mari, A. Segura and A. Chevy, Electrical properties of neutron-transmutation-doped InSe 50 (1991) 415
- L. Roberts and G. Hughes, An investigation of metal/GaAs(100) interfaces by deep level transient spectroscopy 50 (1991) 424
- D. Ashenford, J.H.C. Hogg, B. Lunn and C.G. Scott, The relationship between electrical and structural characteristics of CdTe and CdMnTe layers grown on InSb 50 (1991) 440
- L.J. Bredell, F.D. Aurret, G. Myburg and W.O. Barnard, Electrical characterization of argon-ion sputtered n-GaAs 50 (1991) 466
- H.-G. Hettwer, W. Lerch, B. Lentfort, N.A. Stolwijk and H. Mehrer, Combined application of spreading-resistance and electron-microprobe depth profiling on GaAs:Zn and Si:P 50 (1991) 470
- W. Jantz, R. Stibal, J. Windscheif and J. Wagner, Variation of material parameters along the growth direction of liquid encapsulated Czochralski grown GaAs ingots 50 (1991) 480
- A. Castaldini, A. Cavallini, E. Gombia, R. Mosca and L. Tarricone, Evaluation of the diffusion length of minority carriers in bulk GaAs 50 (1991) 485
- N. Hizem, G. Bremond, L. Mayet, M. Gavand, J. Gregoire, G. Guillot and W. Ulrici, Identification of the double and single acceptor state of isolated Ni_{Ga} in GaAs 50 (1991) 490
- M. Morsli, A. Bonnet, Y. Tregouet, A. Conan, S. Jobic and R. Brec, Electronic properties and band structure of $IrSe_2$ 50 (1991) 500
- Electron bombardment*
- C. Levade, J.J. Couderc, G. Vanderschaeve, D. Caillard and A. Couret, TEM in-situ observation of recombination-enhanced mobility of dislocations in II-VI compounds 50 (1991) 119
- Y. Gao, I. Ardelean, D. Renard, B. Rose and Y. Jin, High-depth-resolution

- SIMS analysis for InGaAs/InP interfaces 50 (1991) 131
- Electron diffraction*
- H. Cerva, Transmission electron microscopy of heteroepitaxial layer structures 50 (1991) 19
- C.T. Foxon, Control of MBE, MOMBE and CBE growth using RHEED 50 (1991) 28
- J. Tardy, I. Thomas, P. Viktorovitch, M. Gendry, J.L. Perrossier, C. Santinelli, M.P. Besland, P. Louis and G. Post, Long-term stability of InP MIS devices 50 (1991) 383
- D. Lee, S.J. Barnett, A.D. Pitt, M.R. Houlton and G.W. Smith, Characterization of alloy composition in $\text{Ga}_{1-x}\text{Al}_x\text{As}$ /GaAs structures: comparison of photovoltage, X-ray, SIMS and RHEED techniques 50 (1991) 428
- D.A. Woolf, D.I. Westwood, M.A. Anderson and R.H. Williams, The molecular beam epitaxial growth of GaAs(111)/Si(111): a variable growth temperature study 50 (1991) 445
- Electron microscopy*
- H. Cerva, Transmission electron microscopy of heteroepitaxial layer structures 50 (1991) 19
- I.T. McGovern, Soft X-ray photoelectron spectroscopy of compound semiconductor surfaces and interfaces 50 (1991) 34
- P. Auvray, A. Poudoulec, M. Baudet, B. Guenais, A. Regreny, C. d'Anter-roches and J. Massies, Interface roughness of GaAs/AlAs superlattices MBE-grown on vicinal surfaces 50 (1991) 109
- C. Frigeri, J.L. Weyher and M. De Potter, TEM study of the origin of the surface microroughness in DSL photoetched Si-implanted GaAs wafers 50 (1991) 115
- C. Levade, J.J. Couderc, G. Vander-schaeve, D. Caillard and A. Couret, TEM in-situ observation of recombination-enhanced mobility of dislocations in II-VI compounds 50 (1991) 119
- P. Ossart and E.V.K. Rao, Investigation of surface and sub-surface defects on polished InP substrates using Auger electron spectroscopy coupled to argon ion sputtering 50 (1991) 125
- Y. Gao, I. Ardelean, D. Renard, B. Rose and Y. Jin, High-depth-resolution SIMS analysis for InGaAs/InP interfaces 50 (1991) 131
- J. Schreiber, W. Hergert and S. Hildebrandt, Combined application of SEM-CL and SEM-EBIC for the investigation of compound semiconductors 50 (1991) 181
- A. Dimoulas, A. Deregis, G. Kyriakidis and A. Christou, Alloy disorder effects in III-V ternaries studied by modulation spectroscopy 50 (1991) 353
- C. Raisin, A. Rocher, G. Landa, R. Carles and L. Lassabatiere, GaSb/GaAs heteroepitaxy characterized as a stress-free system 50 (1991) 434
- R. Schwarz, T. Fischer, P. Hanesch, T. Muschik, J. Kolodzey, H. Cerva, H.L. Meyerheim and B.M.U. Scherzer, Limitations of interface sharpness in a-Si:H/a-SiC:H multilayers 50 (1991) 456
- A. Castaldini, A. Cavallini, E. Gombia, R. Mosca and L. Tarricone, Evaluation of the diffusion length of minority carriers in bulk GaAs 50 (1991) 485
- C. De las Heras, I.J. Ferrer and C. Sánchez, Comparison of pyrite thin films obtained from Fe and natural pyrite powder 50 (1991) 505
- Electron spin resonance*
- S.J.C.H.M. van Gisbergen, M. Godlewski, T. Gregorkiewicz and C.A.J. Amerlaan, Interstitial Mn as a new donor in GaP and GaAs: an EPR study 50 (1991) 273
- T. Benchiguer, E. Christoffel, A. Goltzené, B. Mari, B. Meyer and C. Schwab, Donor-acceptor charge transfers in bulk semi-insulating GaAs as revealed by photo-EPR 50 (1991) 277
- B. Meyer, P. Omling and P. Emanuelsson, Landau oscillations in single quantum wells observed by microwave detection 50 (1991) 420
- Ellipsometry*
- K. Jezierski, Z. Gumienny and J. Misiewicz, Reflectometry-aided surface layer investigation 50 (1991) 341
- C. Pickering, N.S. Garawal, D. Lancefield, J.P. Piel and R. Blunt, Non-destructive characterisation of (Ga,In,Al,As,P)-based ternary multilayer structures using spectroscopic ellipsometry 50 (1991) 346

- H.W. Dinges, B. Kempf, H. Burkhard and R. Göbel, Determination of ion beam etching damage on InP by spectroscopic ellipsometry

50 (1991) 359

Etching

- R. Fornari, N. Tchadjou, P. Gall and J.M. Lussert, A study of structural properties of bulk double-doped InP by laser scattering tomography and photoetching

50 (1991) 207

- M. Baumgartner and K. Löhnert, Characterization of si-GaAs wafer quality by room-temperature photoluminescence

50 (1991) 222

- H.P. Zappe and G. Kaufel, Reactive-ion-etch damage in GaAs processing evaluated by a microwave absorption technique

50 (1991) 290

- H.W. Dinges, B. Kempf, H. Burkhard and R. Göbel, Determination of ion beam etching damage on InP by spectroscopic ellipsometry

50 (1991) 359

Field ion microscopy

- R.A.D. Mackenzie, J.A. Liddle and C.R.M. Grovenor, Ultrahigh resolution characterisation of compound semiconductors using pulsed laser atom probe techniques

50 (1991) 196

Gallium antimonide

- C. Raisin, A. Rocher, G. Landa, R. Carles and L. Lassabatiere, GaSb/GaAs heteroepitaxy characterized as a stress-free system

50 (1991) 434

Gallium arsenide

- J. Matsui, Study of strain variation in LEC-grown GaAs bulk crystals by synchrotron radiation X-ray topography

50 (1991) 1

- P.F. Fewster, Multicrystal X-ray diffraction of heteroepitaxial structures

50 (1991) 9

- H. Cerva, Transmission electron microscopy of heteroepitaxial layer structures

50 (1991) 19

- C.T. Foxon, Control of MBE, MOMBE and CBE growth using RHEED

50 (1991) 28

- I.T. McGovern, Soft X-ray photoelectron spectroscopy of compound semiconductor surfaces and interfaces

50 (1991) 34

- C. Grattapain and A.M. Huber, Secondary ion mass spectrometry of dopants and impurities in compound semiconductors: depth profiling of homo- and heterostructure

50 (1991) 42

- H.G. Grimmeiss and M. Kleverman, Electrical and optical defect spectroscopy of compound semiconductors

50 (1991) 52

- R.A. Stradling, Far-infrared spectroscopy of impurities in semiconductors

50 (1991) 65

- G. Abstreiter, Micro-Raman spectroscopy for characterization of semiconductor devices

50 (1991) 73

- J. Wagner, Raman spectroscopy for impurity characterization in III-V semiconductors

50 (1991) 79

- R. Zaus, M. Schuster, H. Göbel and J.-P. Reithmaier, Characterization of (In, Ga)As/GaAs strained-layer multiple quantum wells with high-resolution X-ray diffraction and computer simulations

50 (1991) 92

- N. Herres, G. Bender and G. Neumann, Assessment of mismatched epitaxial layers by X-ray rocking curve measurements and simulations

50 (1991) 97

- A.M. Keir, S.J. Barnett, J. Giess, T.D. Walsh and M.G. Astles, A combination of high-resolution X-ray diffractometry and diffraction imaging techniques applied to the study of MOVPE-grown $\text{Cd}_x\text{Hg}_{1-x}\text{Te}$ /CdTe on GaAs

50 (1991) 103

- P. Auvray, A. Poudoulec, M. Baudet, B. Guenais, A. Regreny, C. d'Anterches and J. Massies, Interface roughness of GaAs/AlAs superlattices MBE-grown on vicinal surfaces

50 (1991) 109

- C. Frigeri, J.L. Weyher and M. De Potter, TEM study of the origin of the surface microroughness in DSL photoetched Si-implanted GaAs wafers

50 (1991) 115

- T.S. Horányi, P. Tüttő and G. Endrédi, Improved method for depth profiling of multilayer structures

50 (1991) 143

- J.S. Rimmer, M. Missous and A.R. Peaker, A new, fast method for the computer simulation of CV profiles in multilayer structures

50 (1991) 149

- W. Pfeiffer, M. Deicher, R. Keller, R. Magerle, P. Pross, H. Skudlik, Th. Wichert, H. Wolf, D. Forkel, N.

- Moriya and R. Kalish, Characterization of Cd implanted and annealed GaAs and InP by perturbed angular correlation (PAC) spectroscopy 50 (1991) 154
- A. Baurichter, M. Deicher, S. Deubler, D. Forkel, J. Meier, H. Wolf, W. Wittmann and ISOLDE Collaboration, Microscopical studies at cadmium impurities in compound semiconductors 50 (1991) 165
- J. Schreiber, W. Hergert and S. Hildebrandt, Combined application of SEM-CL and SEM-EBIC for the investigation of compound semiconductors 50 (1991) 181
- M. Baumgartner and K. Löhnert, Characterization of si-GaAs wafer quality by room-temperature photoluminescence 50 (1991) 222
- Z.M. Wang, J. Windscheif, D.J. As and W. Jantz, Ambient and low temperature photoluminescence topography of GaAs substrates, epitaxial and implanted layers 50 (1991) 228
- N. Ohnishi, Y. Makita, A. Yamada, H. Asakura and T. Matsumori, Effect of substrate orientation on the defect-induced bound exciton emissions in GaAs grown by molecular beam epitaxy 50 (1991) 233
- G. Strasser, S. Dubois, M. Besson, E. Gornik, G. Weimann, E. Bauser and H. Riechert, Analysis of impurity distribution in n-GaAs layers by photoconductivity and cyclotron resonance measurements 50 (1991) 261
- D.I. Desnica, B. Šantić and U.V. Desnica, Time-evolution of low-temperature photoconductivity and Hall mobility in semi-insulating GaAs 50 (1991) 269
- S.J.C.H.M. van Gisbergen, M. Godlewski, T. Gregorkiewicz and C.A.J. Ammerlaan, Interstitial Mn as a new donor in GaP and GaAs: an EPR study 50 (1991) 273
- T. Benchiguer, E. Christoffel, A. Goltzené, B. Mari, B. Meyer and C. Schwab, Donor-acceptor charge transfers in bulk semi-insulating GaAs as revealed by photo-EPR 50 (1991) 277
- H.P. Zappe and G. Kaufel, Reactive-ion-etch damage in GaAs processing evaluated by a microwave absorption technique 50 (1991) 290
- B.H. Bairamov, V.A. Voitenko, I.P. Ipatova, V.V. Toporov, G. Irmer, J. Monecke and E. Jahne, Characterization of III-V compounds by quasi-elastic electronic scattering of light 50 (1991) 300
- G.M. O'Connor, C.J. McDonagh, F.G. Anderson, T.J. Glynn, G.P. Morgan, G.J. Hughes, L. Roberts and M.O. Henry, Raman characterization of passivated GaAs surfaces 50 (1991) 312
- B. Jusserand and F. Molloy, Confined optical vibrations: a new probe for alloy disorder 50 (1991) 317
- W. Kütt, G.C. Cho, M. Strahlen and H. Kurz, Electro-optic sampling of surface space-charge fields on III-V compounds 50 (1991) 325
- P.L. Swart, B.M. Lacquet and R. Thavar, Physical characterization of OMVPE-grown $\text{Al}_x\text{Ga}_{1-x}\text{As}$ multi-layer films by means of non-destructive optical reflectometry 50 (1991) 330
- S.C. Moss, J.F. Knudsen, R.C. Bowman, Jr., P.M. Adams and D.D. Smith, Picosecond transient photoreflectance measurements of ion-implanted GaAs 50 (1991) 337
- K. Jezierski, Z. Gumienny and J. Misiewicz, Reflectometry-aided surface layer investigation 50 (1991) 341
- C. Pickering, N.S. Garawal, D. Lancefield, J.P. Piel and R. Blunt, Non-destructive characterisation of (Ga,In,Al,As,P)-based ternary multilayer structures using spectroscopic ellipsometry 50 (1991) 346
- A. Dimoulas, A. Dereks, G. Kyriakidis and A. Christou, Alloy disorder effects in III-V ternaries studied by modulation spectroscopy 50 (1991) 353
- B. Sartorius, M. Brandstätter and H. Venghaus, Two-wavelength transmission: a rapid and precise method for measuring the light absorption in semiconductors 50 (1991) 369
- M. Wagner, N. Winkler and H.D. Geiler, Single-beam thermowave analysis of semiconductors 50 (1991) 373
- A.W.R. Leitch, Th. Prescha and M. Stutzmann, Hydrogen passivation and reactivation of shallow Zn acceptors in GaAs 50 (1991) 390
- S. Tüzemen and M.R. Brozel, An investigation of photo-quenching properties of LEC GaAs by using optical and electrical techniques 50 (1991) 395
- C. Ghezzi, R. Mosca, A. Bosacchi, S. Franchi and E. Gombia, The influence of the DX center on the capacitance of Schottky barriers in n-type AlGaAs 50 (1991) 400

- A. Baraldi, C. Ghezzi, A. Parisini, A. Bosacchi and S. Franchi, Analysis of electron mobility versus temperature after photoexcitation in Si-doped $\text{Al}_x\text{Ga}_{1-x}\text{As}$ 50 (1991) 405
- R. Nipoti, D. Poci, A. Cetronio and C. Lanzieri, Carrier and mobility profile measurements in n-type ion-implanted GaAs by the differential sheet resistivity and Hall effect technique 50 (1991) 410
- B. Meyer, P. Omling and P. Emanuelsson, Landau oscillations in single quantum wells observed by microwave detection 50 (1991) 420
- L. Roberts and G. Hughes, An investigation of metal/GaAs(100) interfaces by deep level transient spectroscopy 50 (1991) 424
- D. Lee, S.J. Barnett, A.D. Pitt, M.R. Houlton and G.W. Smith, Characterization of alloy composition in $\text{Ga}_{1-x}\text{Al}_x\text{As}$ /GaAs structures: comparison of photovoltage, X-ray, SIMS and RHEED techniques 50 (1991) 428
- C. Raisin, A. Rocher, G. Landa, R. Carles and L. Lassabatre, GaSb/GaAs heteroepitaxy characterized as a stress-free system 50 (1991) 434
- D.A. Woolf, D.I. Westwood, M.A. Anderson and R.H. Williams, The molecular beam epitaxial growth of GaAs(111)/Si(111): a variable growth temperature study 50 (1991) 445
- V. Amarger, C. Dubon-Chevallier, A.C. Papadopoulos, B. Descouts and Y. Gao, Correlated use of characterization techniques to optimize the Mg implantation annealing for self-aligned HBT's 50 (1991) 462
- L.J. Bredell, F.D. Aurret, G. Myburg and W.O. Barnard, Electrical characterization of argon-ion sputtered n-GaAs 50 (1991) 466
- H.-G. Hettwer, W. Lerch, B. Lentfort, N.A. Stolwijk and H. Mehrer, Combined application of spreading-resistance and electron-microprobe depth profiling on GaAs:Zn and Si:P 50 (1991) 470
- M.R. Brozel, L. Breivik, D.J. Stirling, G.M. Williams and A.G. Cullis, Dislocation density, infrared absorption and cathodoluminescence mapping of microstructure associated with dislocation cells in semi-insulating LEC GaAs 50 (1991) 475
- W. Jantz, R. Stibal, J. Windscheif and J. Wagner, Variation of material parameters along the growth direction of liquid encapsulated Czochralski grown GaAs ingots 50 (1991) 480
- A. Castaldini, A. Cavallini, E. Gombia, R. Mosca and L. Tarricone, Evaluation of the diffusion length of minority carriers in bulk GaAs 50 (1991) 485
- N. Hizem, G. Bremond, L. Mayet, M. Gavand, J. Gregoire, G. Guillot and W. Ulrici, Identification of the double and single acceptor state of isolated Ni_{Ga} in GaAs 50 (1991) 490
- ### Gallium phosphide
- I.T. McGovern, Soft X-ray photoelectron spectroscopy of compound semiconductor surfaces and interfaces 50 (1991) 34
- A. Baurichter, M. Deicher, S. Deubler, D. Forkel, J. Meier, H. Wolf, W. Wittmann and ISOLDE Collaboration, Microscopical studies at cadmium impurities in compound semiconductors 50 (1991) 165
- S.G. Jahn, H. Hofäss, U. Wahl, S. Winter, E. Recknagel and ISOLDE Collaboration, Structural defect recovery in GaP after heavy ion implantation 50 (1991) 169
- A. Gustafsson, S. Nilsson and L. Samuelson, Intensity variations in the near-band-edge recombination of GaP epitaxial layers, grown on (111) and (001) oriented substrates, as observed by cathodoluminescence imaging 50 (1991) 186
- B.J. Heijmink Liesert, M. Godlewski, T. Gregorkiewicz and C.A.J. Ammerlaan, Neutron transmutation doping of GaP: optical studies 50 (1991) 245
- T. Monteiro and E. Pereira, Complex formation in Mn-doped GaP samples 50 (1991) 253
- S.J.C.H.M. van Gisbergen, M. Godlewski, T. Gregorkiewicz and C.A.J. Ammerlaan, Interstitial Mn as a new donor in GaP and GaAs: an EPR study 50 (1991) 273
- P. Roura, J.R. Morante, G. Bremond, T. Benyattou, G. Guillot and W. Ulrici, Complete identification of the Ti-related levels in GaP 50 (1991) 496
- ### Germanium
- P.F. Fewster, Multicrystal X-ray diffraction of heteroepitaxial structures 50 (1991) 9
- H.G. Grimmeiss and M. Kleverman, Electrical and optical defect spectroscopy of compound semiconductors 50 (1991) 52
- B.J. Heijmink Liesert, M. Godlewski, T. Gregorkiewicz and C.A.J. Ammerlaan, Neutron transmutation doping of GaP: optical studies 50 (1991) 245

- M. Mendik, M. Ospelt, H. von Känel and P. Wachter, Determination of elastic properties of Si/Ge superlattices and $\text{Si}_{1-x}\text{Ge}_x$ films from surface acoustic modes by Brillouin scattering 50 (1991) 303
- B. Holländer, S. Mantl, B. Stritzker, F. Schäffler, H.-J. Herzog and E. Kasper, Strain and defect densities in Si/Si $_{1-x}\text{Ge}_x$ heterostructures investigated by ion scattering and X-ray diffraction 50 (1991) 450

Gold

- C. Ghezzi, R. Mosca, A. Bosacchi, S. Franchi and E. Gombia, The influence of the DX center on the capacitance of Schottky barriers in n-type AlGaAs 50 (1991) 400
- L. Roberts and G. Hughes, An investigation of metal/GaAs(100) interfaces by deep level transient spectroscopy 50 (1991) 424

Hall effect

- G. Strasser, S. Dubois, M. Besson, E. Gornik, G. Weimann, E. Bauser and H. Riechert, Analysis of impurity distribution in n-GaAs layers by photoconductivity and cyclotron resonance measurements 50 (1991) 261
- D.I. Desnica, B. Šantić and U.V. Desnica, Time-evolution of low-temperature photoconductivity and Hall mobility in semi-insulating GaAs 50 (1991) 269
- B. Boudart, B. Prévot and C. Schwab, Free-carrier concentration in n-doped InP crystals determined by Raman scattering measurements 50 (1991) 295
- A. Baraldi, C. Ghezzi, A. Parisini, A. Bosacchi and S. Franchi, Analysis of electron mobility versus temperature after photoexcitation in Si-doped $\text{Al}_x\text{Ga}_{1-x}\text{As}$ 50 (1991) 405
- R. Nipoti, D. Pocci, A. Cetronio and C. Lanzieri, Carrier and mobility profile measurements in n-type ion-implanted GaAs by the differential sheet resistivity and Hall effect technique 50 (1991) 410
- B. Mari, A. Segura and A. Chevy, Electrical properties of neutron-transmutation-doped InSe 50 (1991) 415
- D.A. Woolf, D.I. Westwood, M.A. Anderson and R.H. Williams, The molecular beam epitaxial growth of GaAs($\bar{1}\bar{1}\bar{1}$)/Si(111): a variable growth temperature study 50 (1991) 445

Heterostructures

- H. Cerva, Transmission electron microscopy of heteroepitaxial layer structures 50 (1991) 19
- I.T. McGovern, Soft X-ray photoelectron spectroscopy of compound semiconductor surfaces and interfaces 50 (1991) 34
- B. Deveaud, Subpicosecond luminescence spectroscopy of heterostructures (Extended Abstract) 50 (1991) 63
- N. Herres, G. Bender and G. Neumann, Assessment of mismatched epitaxial layers by X-ray rocking curve measurements and simulations 50 (1991) 97
- Y. Gao, I. Ardelean, D. Renard, B. Rose and Y. Jin, High-depth-resolution SIMS analysis for InGaAs/InP interfaces 50 (1991) 131
- T.S. Horányi, P. Tüttő and G. Endrédi, Improved method for depth profiling of multilayer structures 50 (1991) 143
- J.S. Rimmer, M. Missous and A.R. Peaker, A new, fast method for the computer simulation of CV profiles in multilayer structures 50 (1991) 149
- R.A.D. Mackenzie, J.A. Liddle and C.R.M. Grovenor, Ultrahigh resolution characterisation of compound semiconductors using pulsed laser atom probe techniques 50 (1991) 196
- Z.M. Wang, J. Windscheif, D.J. As and W. Jantz, Ambient and low temperature photoluminescence topography of GaAs substrates, epitaxial and implanted layers 50 (1991) 228
- H.P. Zappe and G. Kaufel, Reactive-ion-etch damage in GaAs processing evaluated by a microwave absorption technique 50 (1991) 290
- J.F. Donegan, J.P. Doran, R.P. Stanley, J. Hegarty, R.D. Feldman and R.F. Austin, Resonant Rayleigh scattering from excitons in $\text{Cd}_x\text{Zn}_{1-x}\text{Te}$: ZnTe quantum wells: measurement of homogeneous linewidths 50 (1991) 321
- P.L. Swart, B.M. Lacquet and R. Thavar, Physical characterization of OMVPE-grown $\text{Al}_x\text{Ga}_{1-x}\text{As}$ multi-layer films by means of non-destructive optical reflectometry 50 (1991) 330
- C. Pickering, N.S. Garawal, D. Lancefield, J.P. Piel and R. Blunt, Non-destructive characterisation of (Ga,In,Al,As,P)-based ternary multilayer structures using spectroscopic ellipsometry 50 (1991) 346

- D. Lee, S.J. Barnett, A.D. Pitt, M.R. Houlton and G.W. Smith, Characterization of alloy composition in $\text{Ga}_{1-x}\text{Al}_x\text{As}/\text{GaAs}$ structures: comparison of photovoltage, X-ray, SIMS and RHEED techniques 50 (1991) 428
- B. Holländer, S. Mantl, B. Stritzker, F. Schäffler, H.-J. Herzog and E. Kasper, Strain and defect densities in $\text{Si}/\text{Si}_{1-x}\text{Ge}_x$ heterostructures investigated by ion scattering and X-ray diffraction 50 (1991) 450
- R. Schwarz, T. Fischer, P. Hanesch, T. Muschik, J. Kolodzey, H. Cerva, H.L. Meyerheim and B.M.U. Scherzer, Limitations of interface sharpness in a-Si:H/a-SiC:H multilayers 50 (1991) 456
- Hydrogen**
- V.Kh. Kudoyarova, G.M. Gusinsky, L.A. Rassadin and I.V. Kudryavtsev, Hydrogen depth profile measurement in a- $\text{Si}_{1-x}\text{C}_x\text{:H}$ films by elastic recoil detection 50 (1991) 173
- J. Tatariewicz, A. Kozanecki, Z. Kaliński and K. Paprocki, Photoluminescence study of proton-implanted $\text{InP}_{1-x}\text{As}_x\text{:Yb}$ 50 (1991) 249
- M. Hage-Ali, B. Yaacoub, S. Mergui, M. Samimi, B. Biglari and P. Siffert, Microscopic defect level characterization of semi-insulating compound semiconductors by TSC and PICTS. Application to the effect of hydrogen in CdTe 50 (1991) 377
- A.W.R. Leitch, Th. Prescha and M. Stutzmann, Hydrogen passivation and reactivation of shallow Zn acceptors in GaAs 50 (1991) 390
- Hydrogen sulphide**
- G.M. O'Connor, C.J. McDonagh, F.G. Anderson, T.J. Glynn, G.P. Morgan, G.J. Hughes, L. Roberts and M.O. Henry, Raman characterization of passivated GaAs surfaces 50 (1991) 312
- Indium**
- R. Magerle, M. Deicher, U. Desnica, R. Keller, W. Pfeiffer, F. Pleiter, H. Skudlik and Th. Wichert, Defects in CdS:In detected by perturbed angular correlation spectroscopy (PAC) 50 (1991) 159
- S.G. Jahn, H. Hofsäss, U. Wahl, S. Winter, E. Recknagel and ISOLDE Collaboration, Structural defect recovery in GaP after heavy ion implantation 50 (1991) 169
- Indium antimonide**
- R.A. Stradling, Far-infrared spectroscopy of impurities in semiconductors 50 (1991) 65
- A. Baurichter, M. Deicher, S. Deubler, D. Forkel, J. Meier, H. Wolf, W. Wittmann and ISOLDE Collaboration, Microscopical studies at cadmium impurities in compound semiconductors 50 (1991) 165
- D. Ashenford, J.H.C. Hogg, B. Lunn and C.G. Scott, The relationship between electrical and structural characteristics of CdTe and CdMnTe layers grown on InSb 50 (1991) 440
- Indium arsenide**
- R.A. Stradling, Far-infrared spectroscopy of impurities in semiconductors 50 (1991) 65
- R. Zaus, M. Schuster, H. Göbel and J.-P. Reithmaier, Characterization of (In, Ga)As/GaAs strained-layer multiple quantum wells with high-resolution X-ray diffraction and computer simulations 50 (1991) 92
- A. Baurichter, M. Deicher, S. Deubler, D. Forkel, J. Meier, H. Wolf, W. Wittmann and ISOLDE Collaboration, Microscopical studies at cadmium impurities in compound semiconductors 50 (1991) 165
- B. Meyer, P. Omling and P. Emanuelsson, Landau oscillations in single quantum wells observed by microwave detection 50 (1991) 420
- Indium phosphide**
- I.T. McGovern, Soft X-ray photoelectron spectroscopy of compound semiconductor surfaces and interfaces 50 (1991) 34
- C. Grattapain and A.M. Huber, Secondary ion mass spectrometry of dopants and impurities in compound semiconductors: depth profiling of homo- and heterostructure 50 (1991) 42
- R.A. Stradling, Far-infrared spectroscopy of impurities in semiconductors 50 (1991) 65
- N. Herres, G. Bender and G. Neumann, Assessment of mismatched epitaxial layers by X-ray rocking curve measurements and simulations 50 (1991) 97

- P. Ossart and E.V.K. Rao, Investigation of surface and sub-surface defects on polished InP substrates using Auger electron spectroscopy coupled to argon ion sputtering 50 (1991) 125
- Y. Gao, I. Ardelean, D. Renard, B. Rose and Y. Jin, High-depth-resolution SIMS analysis for InGaAs/InP interfaces 50 (1991) 131
- J.G. Bauer, R. Treichler, T. Hillmer, J. Müller and G. Ebbinghaus, Optimization of Zn dopant profiles in a pin-diode/FET by combination of depth profiling techniques: a SIMS, ECV and AES study 50 (1991) 138
- W. Pfeiffer, M. Deicher, R. Keller, R. Magerle, P. Pross, H. Skudlik, Th. Wichert, H. Wolf, D. Forkel, N. Moriya and R. Kalish, Characterization of Cd implanted and annealed GaAs and InP by perturbed angular correlation (PAC) spectroscopy 50 (1991) 154
- A. Baurichter, M. Deicher, S. Deubler, D. Forkel, J. Meier, H. Wolf, W. Witthuhn and ISOLDE Collaboration, Microscopical studies at cadmium impurities in compound semiconductors 50 (1991) 165
- B.L. Chen, M. Eckstein and H.-U. Haberman, Cathodoluminescence investigations of RIE-induced defects in InP 50 (1991) 191
- R. Fornari, N. Tchandjou, P. Gall and J.M. Lussert, A study of structural properties of bulk double-doped InP by laser scattering tomography and photoetching 50 (1991) 207
- H. L'Haridon, P.N. Favenne, R. Coquille, M. Salvi, M. Gauneau, Y. Le Guillou, R. Callec and P. Gall, Spatial investigation of an iron-doped indium phosphide ingot 50 (1991) 237
- J. Tatarkiewicz, A. Kozanecki, Z. Kaliński and K. Paprocki, Photoluminescence study of proton-implanted $\text{InP}_{1-x}\text{As}_x\text{Yb}$ 50 (1991) 249
- G.M. Crean, P.A.F. Herbert, I. Little, W.M. Kelly, J.Y. Marzin, A. Izrael and B. Jusserand, Investigation of reactive ion etch-induced damage in InP surfaces using a noncontact photo-thermal radiometric probe 50 (1991) 281
- B. Boudart, B. Prévot and C. Schwab, Free-carrier concentration in n-doped InP crystals determined by Raman scattering measurements 50 (1991) 295
- B.H. Bairamov, V.A. Voitenko, I.P. Ipatova, V.V. Toporov, G. Irmer, J. Monecke and E. Jahne, Characterization of III-V compounds by quasi-elastic electronic scattering of light 50 (1991) 300
- C. Pickering, N.S. Garawal, D. Lancefield, J.P. Piel and R. Blunt, Non-destructive characterisation of (Ga,In,Al,As,P)-based ternary multilayer structures using spectroscopic ellipsometry 50 (1991) 346
- A. Dimoulas, A. Derekis, G. Kyriakidis and A. Christou, Alloy disorder effects in III-V ternaries studied by modulation spectroscopy 50 (1991) 353
- H.W. Dinges, B. Kempf, H. Burkhard and R. Göbel, Determination of ion beam etching damage on InP by spectroscopic ellipsometry 50 (1991) 359
- F. Mosel, A. Seidl, D. Hofmann and G. Müller, Infrared absorption of n- and p-type Fe-doped InP and mapping of the Fe distribution 50 (1991) 364
- B. Sartorius, M. Brandstättnr and H. Venghaus, Two-wavelength transmission: a rapid and precise method for measuring the light absorption in semiconductors 50 (1991) 369
- J. Tardy, I. Thomas, P. Viktorovitch, M. Gendry, J.L. Perrossier, C. Santinelli, M.P. Besland, P. Louis and G. Post, Long-term stability of InP MIS devices 50 (1991) 383
- B. Meyer, P. Omling and P. Emanuelsson, Landau oscillations in single quantum wells observed by microwave detection 50 (1991) 420
- Infrared spectroscopy*
- R.A. Stradling, Far-infrared spectroscopy of impurities in semiconductors 50 (1991) 65
- V.Kh. Kudoyarova, G.M. Gusinsky, L.A. Rassadin and I.V. Kudryavtsev, Hydrogen depth profile measurement in $\text{a-Si}_{1-x}\text{C}_x\text{:H}$ films by elastic recoil detection 50 (1991) 173
- A. Deneuve, D.B. Tanner, R.M. Park and P.H. Holloway, Semiconductor electrical properties from the frequency dependence of the dielectric constant: application to n-type ZnSe heteroepitaxial thin films 50 (1991) 285
- F. Mosel, A. Seidl, D. Hofmann and G. Müller, Infrared absorption of n- and p-type Fe-doped InP and mapping of the Fe distribution 50 (1991) 364
- R. Schwarz, T. Fischer, P. Hanesch, T. Muschik, J. Kolodzey, H. Cerva, H.L.

- Meyerheim and B.M.U. Scherzer, Limitations of interface sharpness in a-Si:H/a-SiC:H multilayers 50 (1991) 456
- M.R. Brozel, L. Breivik, D.J. Stirland, G.M. Williams and A.G. Cullis, Dislocation density, infrared absorption and cathodoluminescence mapping of microstructure associated with dislocation cells in semi-insulating LEC GaAs 50 (1991) 475
- Ion bombardment*
- H.W. Dinges, B. Kempf, H. Burkhard and R. Göbel, Determination of ion beam etching damage on InP by spectroscopic ellipsometry 50 (1991) 359
- Ion implantation*
- J. Wagner, Raman spectroscopy for impurity characterization in III-V semiconductors 50 (1991) 79
- C. Frigeri, J.L. Weyher and M. De Potter, TEM study of the origin of the surface microroughness in DSL photoetched Si-implanted GaAs wafers 50 (1991) 115
- W. Pfeiffer, M. Deicher, R. Keller, R. Magerle, P. Pross, H. Skudlik, Th. Wichert, H. Wolf, D. Forkel, N. Moriya and R. Kalish, Characterization of Cd implanted and annealed GaAs and InP by perturbed angular correlation (PAC) spectroscopy 50 (1991) 154
- S.G. Jahn, H. Hofsäuss, U. Wahl, S. Winter, E. Recknagel and ISOLDE Collaboration, Structural defect recovery in GaP after heavy ion implantation 50 (1991) 169
- Z.M. Wang, J. Windscheif, D.J. As and W. Jantz, Ambient and low temperature photoluminescence topography of GaAs substrates, epitaxial and implanted layers 50 (1991) 228
- H. L'Haridon, P.N. Favennec, R. Coquille, M. Salvi, M. Gauneau, Y. Le Guillou, R. Callec and P. Gall, Spatial investigation of an iron-doped indium phosphide ingot 50 (1991) 237
- J. Tatarkiewicz, A. Kozanecki, Z. Kaliński and K. Paprocki, Photoluminescence study of proton-implanted $\text{InP}_{1-x}\text{As}_x\text{:Yb}$ 50 (1991) 249
- A. Deneuville, C.H. Park, P. Ayyub, T. Anderson, P. Lowen, K. Jones and P.H. Holloway, O implantation in ZnSe: lattice distortion by Raman measurement 50 (1991) 308
- S.C. Moss, J.F. Knudsen, R.C. Bowman, Jr., P.M. Adams and D.D. Smith, Picosecond transient photoreflectance measurements of ion-implanted GaAs 50 (1991) 337
- M. Wagner, N. Winkler and H.D. Geiler, Single-beam thermowave analysis of semiconductors 50 (1991) 373
- M. Hage-Ali, B. Yaacoub, S. Mergui, M. Samimi, B. Biglari and P. Siffert, Microscopic defect level characterization of semi-insulating compound semiconductors by TSC and PICTS. Application to the effect of hydrogen in CdTe 50 (1991) 377
- R. Nipoti, D. Pucci, A. Cetronio and C. Lanzieri, Carrier and mobility profile measurements in n-type ion-implanted GaAs by the differential sheet resistivity and Hall effect technique 50 (1991) 410
- V. Amarger, C. Dubon-Chevallier, A.C. Papadopoulos, B. Descouts and Y. Gao, Correlated use of characterization techniques to optimize the Mg implantation annealing for self-aligned HBT's 50 (1991) 462
- Ion scattering*
- V.Kh. Kudoyarova, G.M. Gusinsky, L.A. Rassadin and I.V. Kudryavtsev, Hydrogen depth profile measurement in a-Si_{1-x}C_x:H films by elastic recoil detection 50 (1991) 173
- B. Holländer, S. Mantl, B. Stritzker, F. Schäffler, H.-J. Herzog and E. Kasper, Strain and defect densities in Si/Si_{1-x}Ge_x heterostructures investigated by ion scattering and X-ray diffraction 50 (1991) 450
- R. Schwarz, T. Fischer, P. Hanesch, T. Muschik, J. Kolodzey, H. Cerva, H.L. Meyerheim and B.M.U. Scherzer, Limitations of interface sharpness in a-Si:H/a-SiC:H multilayers 50 (1991) 456
- Iron*
- H. L'Haridon, P.N. Favennec, R. Coquille, M. Salvi, M. Gauneau, Y. Le Guillou, R. Callec and P. Gall, Spatial investigation of an iron-doped indium phosphide ingot 50 (1991) 237
- F. Mosel, A. Seidl, D. Hofmann and G. Müller, Infrared absorption of n- and p-type Fe-doped InP and mapping of the Fe distribution 50 (1991) 364
- B. Sartorius, M. Brandstättnner and H. Venghaus, Two-wavelength transmis-

sion: a rapid and precise method for measuring the light absorption in semiconductors

- L. Roberts and G. Hughes, An investigation of metal/GaAs(100) interfaces by deep level transient spectroscopy
C. De las Heras, I.J. Ferrer and C. Sánchez, Comparison of pyrite thin films obtained from Fe and natural pyrite powder

Lanthanides

- J. Tatarkiewicz, A. Kozanecki, Z. Kaliński and K. Paprocki, Photoluminescence study of proton-implanted $\text{InP}_{1-x}\text{As}_x\text{:Yb}$

Light scattering

- R. Fornari, N. Tchandjou, P. Gall and J.M. Lussert, A study of structural properties of bulk double-doped InP by laser scattering tomography and photoetching
B.H. Bairamov, V.A. Voitenko, I.P. Ipatova, V.V. Toporov, G. Irmer, J. Monecke and E. Jahne, Characterization of III-V compounds by quasi-elastic electronic scattering of light
M. Mendik, M. Ospelt, H. von Känel and P. Wachter, Determination of elastic properties of Si/Ge superlattices and $\text{Si}_{1-x}\text{Ge}_x$ films from surface acoustic modes by Brillouin scattering
J.F. Donegan, J.P. Doran, R.P. Stanley, J. Hegarty, R.D. Feldman and R.F. Austin, Resonant Rayleigh scattering from excitons in $\text{Cd}_x\text{Zn}_{1-x}\text{Te:ZnTe}$ quantum wells: measurement of homogeneous linewidths
W. Kütt, G.C. Cho, M. Strahnen and H. Kurz, Electro-optic sampling of surface space-charge fields on III-V compounds
S.C. Moss, J.F. Knudsen, R.C. Bowman, Jr., P.M. Adams and D.D. Smith, Picosecond transient photoreflectance measurements of ion-implanted GaAs
B. Sartorius, M. Brandstätter and H. Venghaus, Two-wavelength transmission: a rapid and precise method for measuring the light absorption in semiconductors
M. Wagner, N. Winkler and H.D. Geiler, Single-beam thermowave analysis of semiconductors

Luminescence

- B. Deveaud, Subpicosecond luminescence spectroscopy of heterostructures (Extended Abstract)
J. Schreiber, W. Hergert and S. Hildebrandt, Combined application of SEM-CL and SEM-EBIC for the investigation of compound semiconductors
A. Gustafsson, S. Nilsson and L. Samuelson, Intensity variations in the near-band-edge recombination of GaP epitaxial layers, grown on (111) and (001) oriented substrates, as observed by cathodoluminescence imaging
B.L. Chen, M. Eckstein and H.-U. Haberman, Cathodoluminescence investigations of RIE-induced defects in InP
J.C. Fariñas and M.F. Barba, Inductively coupled plasma-atomic emission spectrometry (ICP-AES): an analytical technique for the chemical characterization of perovskite ceramic semiconductors
A. Antolini and C. Lamberti, Computing errors in Fourier transform photoluminescence
M. Baumgartner and K. Löhnert, Characterization of si-GaAs wafer quality by room-temperature photoluminescence
Z.M. Wang, J. Windscheif, D.J. As and W. Jantz, Ambient and low temperature photoluminescence topography of GaAs substrates, epitaxial and implanted layers
N. Ohnishi, Y. Makita, A. Yamada, H. Asakura and T. Matsumori, Effect of substrate orientation on the defect-induced bound exciton emissions in GaAs grown by molecular beam epitaxy
H. L'Haridon, P.N. Favenec, R. Coquille, M. Salvi, M. Gauneau, Y. Le Guillou, R. Callec and P. Gall, Spatial investigation of an iron-doped indium phosphide ingot
B.J. Heijmink Liesert, M. Godlewski, T. Gregorkiewicz and C.A.J. Ammerlaan, Neutron transmutation doping of GaP: optical studies
J. Tatarkiewicz, A. Kozanecki, Z. Kaliński and K. Paprocki, Photoluminescence study of proton-implanted $\text{InP}_{1-x}\text{As}_x\text{:Yb}$

- T. Monteiro and E. Pereira, Complex formation in Mn-doped GaP samples 50 (1991) 253
- A. Zakrzewski and M. Godlewski, Three-center Auger effect and the quantum yield of the luminescence of ZnS-based phosphors 50 (1991) 257
- G.M. Crean, P.A.F. Herbert, I. Little, W.M. Kelly, J.Y. Marzin, A. Izrael and B. Jusserand, Investigation of reactive ion etch-induced damage in InP surfaces using a noncontact photo-thermal radiometric probe 50 (1991) 281
- V. Amarger, C. Dubon-Chevallier, A.C. Papadopoulos, B. Descouts and Y. Gao, Correlated use of characterization techniques to optimize the Mg implantation annealing for self-aligned HBT's 50 (1991) 462
- M.R. Brozel, L. Breivik, D.J. Stirland, G.M. Williams and A.G. Cullis, Dislocation density, infrared absorption and cathodoluminescence mapping of microstructure associated with dislocation cells in semi-insulating LEC GaAs 50 (1991) 475
- W. Jantz, R. Stibal, J. Windscheif and J. Wagner, Variation of material parameters along the growth direction of liquid encapsulated Czochralski grown GaAs ingots 50 (1991) 480
- Magnesium**
- V. Amarger, C. Dubon-Chevallier, A.C. Papadopoulos, B. Descouts and Y. Gao, Correlated use of characterization techniques to optimize the Mg implantation annealing for self-aligned HBT's 50 (1991) 462
- Magnetic measurements**
- H.G. Grimmeiss and M. Kleverman, Electrical and optical defect spectroscopy of compound semiconductors 50 (1991) 52
- R.A. Stradling, Far-infrared spectroscopy of impurities in semiconductors 50 (1991) 65
- B.J. Heijmink Liesert, M. Godlewski, T. Gregorkiewicz and C.A.J. Ammerlaan, Neutron transmutation doping of GaP: optical studies 50 (1991) 245
- B. Meyer, P. Omring and P. Emanuelsson, Landau oscillations in single quantum wells observed by microwave detection 50 (1991) 420
- Manganese**
- H.G. Grimmeiss and M. Kleverman, Electrical and optical defect spectroscopy of compound semiconductors 50 (1991) 52
- T. Monteiro and E. Pereira, Complex formation in Mn-doped GaP samples 50 (1991) 253
- S.J.C.H.M. van Gisbergen, M. Godlewski, T. Gregorkiewicz and C.A.J. Ammerlaan, Interstitial Mn as a new donor in GaP and GaAs: an EPR study 50 (1991) 273
- Mass spectroscopy**
- R.A.D. Mackenzie, J.A. Liddle and C.R.M. Grovenor, Ultrahigh resolution characterisation of compound semiconductors using pulsed laser atom probe techniques 50 (1991) 196
- Mercury**
- A.M. Keir, S.J. Barnett, J. Giess, T.D. Walsh and M.G. Astles, A combination of high-resolution X-ray diffractometry and diffraction imaging techniques applied to the study of MOVPE-grown $\text{Cd}_x\text{Hg}_{1-x}\text{Te}$ /CdTe on GaAs 50 (1991) 103
- Metal-semiconductor interfaces**
- L. Roberts and G. Hughes, An investigation of metal/GaAs(100) interfaces by deep level transient spectroscopy 50 (1991) 424
- Molecular beam epitaxy**
- C.T. Foxon, Control of MBE, MOMBE and CBE growth using RHEED 50 (1991) 28
- C. Grattepain and A.M. Huber, Secondary ion mass spectrometry of dopants and impurities in compound semiconductors: depth profiling of homo- and heterostructure 50 (1991) 42
- R. Zaus, M. Schuster, H. Göbel and J.-P. Reithmaier, Characterization of (In, Ga)As/GaAs strained-layer multiple quantum wells with high-resolution X-ray diffraction and computer simulations 50 (1991) 92

- P. Auvray, A. Poudoulec, M. Baudet, B. Guenais, A. Regreny, C. d'Anter-
roches and J. Massies, Interface
roughness of GaAs/AlAs super-
lattices MBE-grown on vicinal surfaces 50 (1991) 109
- N. Ohnishi, Y. Makita, A. Yamada, H.
Asakura and T. Matsumori, Effect of
substrate orientation on the defect-in-
duced bound exciton emissions in
GaAs grown by molecular beam epi-
taxy 50 (1991) 233
- B. Jusserand and F. Molloy, Confined
optical vibrations: a new probe for
alloy disorder 50 (1991) 317
- C. Ghezzi, R. Mosca, A. Bosacchi, S.
Franchi and E. Gombia, The influence
of the DX center on the capacitance
of Schottky barriers in n-type AlGaAs 50 (1991) 400
- C. Raisin, A. Rocher, G. Landa, R. Carles
and L. Lassabatere, GaSb/GaAs het-
eroepitaxy characterized as a stress-
free system 50 (1991) 434
- D. Ashenford, J.H.C. Hogg, B. Lunn and
C.G. Scott, The relationship between
electrical and structural characteristics
of CdTe and CdMnTe layers grown
on InSb 50 (1991) 440
- D.A. Woolf, D.I. Westwood, M.A. Ander-
son and R.H. Williams, The molecular
beam epitaxial growth of GaAs(111)/
Si(111): a variable growth temperature
study 50 (1991) 445
- B. Holländer, S. Mantl, B. Stritzker, F.
Schäffler, H.-J. Herzog and E. Kasper,
Strain and defect densities in Si/
Si_{1-x}Ge_x heterostructures investigated
by ion scattering and X-ray diffrac-
tion 50 (1991) 450
- MOS (metal-oxide-semiconductor) structure*
- G. Abstreiter, Micro-Raman spectroscopy
for characterization of semiconductor
devices 50 (1991) 73
- J. Tardy, I. Thomas, P. Viktorovitch, M.
Gendry, J.L. Perrossier, C. Santinelli,
M.P. Besland, P. Louis and G. Post,
Long-term stability of InP MIS de-
vices 50 (1991) 383
- Nickel*
- N. Hizem, G. Bremond, L. Mayet, M.
Gavand, J. Gregoire, G. Guillot and
W. Ulrici, Identification of the double
and single acceptor state of isolated
Ni_{Ga} in GaAs 50 (1991) 490
- Noble gases*
- S.C. Moss, J.F. Knudsen, R.C. Bowman,
Jr., P.M. Adams and D.D. Smith, Pi-
cosecond transient photoreflectance
measurements of ion-implanted GaAs 50 (1991) 337
- Optical properties*
- H.G. Grimmeiss and M. Kleverman,
Electrical and optical defect spec-
troscopy of compound semiconduc-
tors 50 (1991) 52
- A. Deneuve, D.B. Tanner, R.M. Park
and P.H. Holloway, Semiconductor
electrical properties from the frequen-
cy dependence of the dielectric con-
stant: application to n-type ZnSe het-
eroepitaxial thin films 50 (1991) 285
- J.F. Donegan, J.P. Doran, R.P. Stanley, J.
Hegarty, R.D. Feldman and R.F.
Austin, Resonant Rayleigh scattering
from excitons in Cd_xZn_{1-x}Te:ZnTe
quantum wells: measurement of ho-
mogeneous linewidths 50 (1991) 321
- W. Kütt, G.C. Cho, M. Strahlen and H.
Kurz, Electro-optic sampling of sur-
face space-charge fields on III-V
compounds 50 (1991) 325
- P.L. Swart, B.M. Lacquet and R. Thavar,
Physical characterization of OMVPE-
grown Al_xGa_{1-x}As multi-layer films
by means of non-destructive optical
reflectometry 50 (1991) 330
- K. Jezierski, Z. Gumienny and J. Mis-
iewicz, Reflectometry-aided surface
layer investigation 50 (1991) 341
- F. Mosel, A. Seidl, D. Hofmann and G.
Müller, Infrared absorption of n- and
p-type Fe-doped InP and mapping of
the Fe distribution 50 (1991) 364
- S. Tüzemen and M.R. Brozel, An investi-
gation of photo-quenching properties
of LEC GaAs by using optical and
electrical techniques 50 (1991) 395
- N. Hizem, G. Bremond, L. Mayet, M.
Gavand, J. Gregoire, G. Guillot and
W. Ulrici, Identification of the double
and single acceptor state of isolated
Ni_{Ga} in GaAs 50 (1991) 490
- P. Roura, J.R. Morante, G. Bremond, T.
Benyattou, G. Guillot and W. Ulrici,

- Complete identification of the Ti-related levels in GaP 50 (1991) 496
- Organometallic vapour deposition*
- C.T. Foxon, Control of MBE, MOMBE and CBE growth using RHEED 50 (1991) 28
- C. Grattapain and A.M. Huber, Secondary ion mass spectrometry of dopants and impurities in compound semiconductors: depth profiling of homo- and heterostructure 50 (1991) 42
- N. Herres, G. Bender and G. Neumann, Assessment of mismatched epitaxial layers by X-ray rocking curve measurements and simulations 50 (1991) 97
- A.M. Keir, S.J. Barnett, J. Giess, T.D. Walsh and M.G. Astles, A combination of high-resolution X-ray diffractometry and diffraction imaging techniques applied to the study of MOVPE-grown $\text{Cd}_x\text{Hg}_{1-x}\text{Te}/\text{CdTe}$ on GaAs 50 (1991) 103
- J.G. Bauer, R. Treichler, T. Hillmer, J. Müller and G. Ebbinghaus, Optimization of Zn dopant profiles in a pin-diode/FET by combination of depth profiling techniques: a SIMS, ECV and AES study 50 (1991) 138
- A. Gustafsson, S. Nilsson and L. Samuelson, Intensity variations in the near-band-edge recombination of GaP epitaxial layers, grown on (111) and (001) oriented substrates, as observed by cathodoluminescence imaging 50 (1991) 186
- Z.M. Wang, J. Windscheif, D.J. As and W. Jantz, Ambient and low temperature photoluminescence topography of GaAs substrates, epitaxial and implanted layers 50 (1991) 228
- P.L. Swart, B.M. Lacquet and R. Thavar, Physical characterization of OMVPE-grown $\text{Al}_x\text{Ga}_{1-x}\text{As}$ multi-layer films by means of non-destructive optical reflectometry 50 (1991) 330
- Oxides*
- J.C. Fariñas and M.F. Barba, Inductively coupled plasma-atomic emission spectrometry (ICP-AES): an analytical technique for the chemical characterization of perovskite ceramic semiconductors 50 (1991) 202
- Oxygen*
- Y. Gao, I. Ardelean, D. Renard, B. Rose and Y. Jin, High-depth-resolution SIMS analysis for InGaAs/InP interfaces 50 (1991) 131
- A. Deneuve, C.H. Park, P. Ayyub, T. Anderson, P. Lowen, K. Jones and P.H. Holloway, O implantation in ZnSe: lattice distortion by Raman measurement 50 (1991) 308
- Phosphorus*
- H.-G. Hettwer, W. Lerch, B. Lentfort, N.A. Stolwijk and H. Mehrer, Combined application of spreading-resistance and electron-microprobe depth profiling on GaAs:Zn and Si:P 50 (1991) 470
- Photoconductivity*
- R.A. Stradling, Far-infrared spectroscopy of impurities in semiconductors 50 (1991) 65
- S.D. Baranovskii, Theoretical basis for the quantitative characterization of impurities in n-type III-V compound semiconductors by photoelectromagnetic spectroscopy 50 (1991) 218
- G. Strasser, S. Dubois, M. Besson, E. Gornik, G. Weimann, E. Bauser and H. Riechert, Analysis of impurity distribution in n-GaAs layers by photoconductivity and cyclotron resonance measurements 50 (1991) 261
- S. Usala, G.J. Adriaenssens, Ö. Öktü and M. Nesladek, Post-transit-time analysis of time-of-flight photocurrents 50 (1991) 265
- D.I. Desnica, B. Šantić and U.V. Desnica, Time-evolution of low-temperature photoconductivity and Hall mobility in semi-insulating GaAs 50 (1991) 269
- M. Hage-Ali, B. Yaacoub, S. Mergui, M. Samimi, B. Biglari and P. Siffert, Microscopic defect level characterization of semi-insulating compound semiconductors by TSC and PICTS. Application to the effect of hydrogen in CdTe 50 (1991) 377
- A. Baraldi, C. Ghezzi, A. Parisini, A. Bosacchi and S. Franchi, Analysis of electron mobility versus temperature after photoexcitation in Si-doped $\text{Al}_x\text{Ga}_{1-x}\text{As}$ 50 (1991) 405

Photoelectron spectroscopy

- I.T. McGovern, Soft X-ray photoelectron spectroscopy of compound semiconductor surfaces and interfaces 50 (1991) 34

Plasma processing

- A. Baurichter, M. Deicher, S. Deubler, D. Forkel, J. Meier, H. Wolf, W. Wittmann and ISOLDE Collaboration, Microscopical studies at cadmium impurities in compound semiconductors 50 (1991) 165
- B.L. Chen, M. Eckstein and H.-U. Haberman, Cathodoluminescence investigations of RIE-induced defects in InP 50 (1991) 191
- G.M. Crean, P.A.F. Herbert, I. Little, W.M. Kelly, J.Y. Marzin, A. Izrael and B. Jusserand, Investigation of reactive ion etch-induced damage in InP surfaces using a noncontact photo-thermal radiometric probe 50 (1991) 281
- H.P. Zappe and G. Kaufel, Reactive-ion-etch damage in GaAs processing evaluated by a microwave absorption technique 50 (1991) 290
- A.W.R. Leitch, Th. Prescha and M. Stutzmann, Hydrogen passivation and reactivation of shallow Zn acceptors in GaAs 50 (1991) 390

Quantum effects

- B. Deveaud, Subpicosecond luminescence spectroscopy of heterostructures (Extended Abstract) 50 (1991) 63
- J.F. Donegan, J.P. Doran, R.P. Stanley, J. Hegarty, R.D. Feldman and R.F. Austin, Resonant Rayleigh scattering from excitons in $\text{Cd}_x\text{Zn}_{1-x}\text{Te}$: ZnTe quantum wells: measurement of homogeneous linewidths 50 (1991) 321
- B. Meyer, P. Omling and P. Emanuelsson, Landau oscillations in single quantum wells observed by microwave detection 50 (1991) 420

Radiation damage

- B.L. Chen, M. Eckstein and H.-U. Haberman, Cathodoluminescence investigations of RIE-induced defects in InP 50 (1991) 191
- J. Tatarkiewicz, A. Kozanecki, Z. Kalif-

- ski and K. Paprocki, Photoluminescence study of proton-implanted $\text{InP}_{1-x}\text{As}_x\text{:Yb}$ 50 (1991) 249
- G.M. Crean, P.A.F. Herbert, I. Little, W.M. Kelly, J.Y. Marzin, A. Izrael and B. Jusserand, Investigation of reactive ion etch-induced damage in InP surfaces using a noncontact photo-thermal radiometric probe 50 (1991) 281
- H.P. Zappe and G. Kaufel, Reactive-ion-etch damage in GaAs processing evaluated by a microwave absorption technique 50 (1991) 290
- H.W. Dinges, B. Kempf, H. Burkhard and R. Göbel, Determination of ion beam etching damage on InP by spectroscopic ellipsometry 50 (1991) 359

Raman scattering

- G. Abstreiter, Micro-Raman spectroscopy for characterization of semiconductor devices 50 (1991) 73
- J. Wagner, Raman spectroscopy for impurity characterization in III-V semiconductors 50 (1991) 79
- G.M. Crean, P.A.F. Herbert, I. Little, W.M. Kelly, J.Y. Marzin, A. Izrael and B. Jusserand, Investigation of reactive ion etch-induced damage in InP surfaces using a noncontact photo-thermal radiometric probe 50 (1991) 281
- B. Boudart, B. Prévot and C. Schwab, Free-carrier concentration in n-doped InP crystals determined by Raman scattering measurements 50 (1991) 295
- B.H. Bairamov, V.A. Voitenko, I.P. Ipatova, V.V. Toporov, G. Irmer, J. Monecke and E. Jahne, Characterization of III-V compounds by quasi-elastic electronic scattering of light 50 (1991) 300
- A. Deneuve, C.H. Park, P. Ayyub, T. Anderson, P. Lowen, K. Jones and P.H. Holloway, O implantation in ZnSe: lattice distortion by Raman measurement 50 (1991) 308
- G.M. O'Connor, C.J. McDonagh, F.G. Anderson, T.J. Glynn, G.P. Morgan, G.J. Hughes, L. Roberts and M.O. Henry, Raman characterization of passivated GaAs surfaces 50 (1991) 312
- B. Jusserand and F. Molloy, Confined optical vibrations: a new probe for alloy disorder 50 (1991) 317
- S.C. Moss, J.F. Knudsen, R.C. Bowman, Jr., P.M. Adams and D.D. Smith, Pi-

- cosecond transient photoreflectance measurements of ion-implanted GaAs 50 (1991) 337
- C. Raisin, A. Rocher, G. Landa, R. Carles and L. Lassabatere, GaSb/GaAs heteroepitaxy characterized as a stress-free system 50 (1991) 434
- Reflection spectroscopy*
- K. Jezierski, Z. Gumienny and J. Misiewicz, Reflectometry-aided surface layer investigation 50 (1991) 341
- A. Dimoulas, A. Derekis, G. Kyriakidis and A. Christou, Alloy disorder effects in III-V ternaries studied by modulation spectroscopy 50 (1991) 353
- Schottky barrier*
- C. Ghezzi, R. Mosca, A. Bosacchi, S. Franchi and E. Gombia, The influence of the DX center on the capacitance of Schottky barriers in n-type AlGaAs 50 (1991) 400
- L. Roberts and G. Hughes, An investigation of metal/GaAs(100) interfaces by deep level transient spectroscopy 50 (1991) 424
- L.J. Bredell, F.D. Aurret, G. Myburg and W.O. Barnard, Electrical characterization of argon-ion sputtered n-GaAs 50 (1991) 466
- Secondary ion mass spectroscopy*
- C. Grattapain and A.M. Huber, Secondary ion mass spectrometry of dopants and impurities in compound semiconductors: depth profiling of homo- and heterostructure 50 (1991) 42
- Y. Gao, I. Ardelean, D. Renard, B. Rose and Y. Jin, High-depth-resolution SIMS analysis for InGaAs/InP interfaces 50 (1991) 131
- J.G. Bauer, R. Treichler, T. Hillmer, J. Müller and G. Ebbinghaus, Optimization of Zn dopant profiles in a pin-diode/FET by combination of depth profiling techniques: a SIMS, ECV and AES study 50 (1991) 138
- H. L'Haridon, P.N. Favenne, R. Coquille, M. Salvi, M. Gauneau, Y. Le Guillou, R. Callec and P. Gall, Spatial investigation of an iron-doped indium phosphide ingot 50 (1991) 237
- P.L. Swart, B.M. Lacquet and R. Thavar, Physical characterization of OMVPE-grown $\text{Al}_x\text{Ga}_{1-x}\text{As}$ multi-layer films by means of non-destructive optical reflectometry 50 (1991) 330
- D. Lee, S.J. Barnett, A.D. Pitt, M.R. Houlton and G.W. Smith, Characterization of alloy composition in $\text{Ga}_{1-x}\text{Al}_x\text{As}$ /GaAs structures: comparison of photovoltage, X-ray, SIMS and RHEED techniques 50 (1991) 428
- V. Amarger, C. Dubon-Chevallier, A.C. Papadopoulos, B. Descouts and Y. Gao, Correlated use of characterization techniques to optimize the Mg implantation annealing for self-aligned HBT's 50 (1991) 462
- P. Roura, J.R. Morante, G. Bremond, T. Benyattou, G. Guillot and W. Ulrici, Complete identification of the Ti-related levels in GaP 50 (1991) 496
- Semiconductor-semiconductor interfaces*
- P.F. Fewster, Multicrystal X-ray diffraction of heteroepitaxial structures 50 (1991) 9
- P. Auvray, A. Poudoulec, M. Baudet, B. Guenais, A. Regreny, C. d'Anterchies and J. Massies, Interface roughness of GaAs/AlAs superlattices MBE-grown on vicinal surfaces 50 (1991) 109
- Y. Gao, I. Ardelean, D. Renard, B. Rose and Y. Jin, High-depth-resolution SIMS analysis for InGaAs/InP interfaces 50 (1991) 131
- J.S. Rimmer, M. Missous and A.R. Peaker, A new, fast method for the computer simulation of CV profiles in multi-layer structures 50 (1991) 149
- B. Jusserand and F. Mollot, Confined optical vibrations: a new probe for alloy disorder 50 (1991) 317
- D.A. Woolf, D.I. Westwood, M.A. Anderson and R.H. Williams, The molecular beam epitaxial growth of GaAs(111)/Si(111): a variable growth temperature study 50 (1991) 445
- Silicon*
- P.F. Fewster, Multicrystal X-ray diffraction of heteroepitaxial structures 50 (1991) 9
- C. Grattapain and A.M. Huber, Secondary ion mass spectrometry of dopants and impurities in compound semiconductors: depth profiling of homo- and heterostructure 50 (1991) 42
- H.G. Grimmeiss and M. Kleverman, Electrical and optical defect spec-

- troscopy of compound semiconductors
- J. Wagner, Raman spectroscopy for impurity characterization in III-V semiconductors 50 (1991) 52
- C. Frigeri, J.L. Weyher and M. De Potter, TEM study of the origin of the surface microroughness in DSL photoetched Si-implanted GaAs wafers 50 (1991) 79
- S. Usala, G.J. Adriaenssens, Ö. Öktü and M. Nesladek, Post-transit-time analysis of time-of-flight photocurrents 50 (1991) 115
- M. Mendik, M. Ospelt, H. von Känel and P. Wachter, Determination of elastic properties of Si/Ge superlattices and $\text{Si}_{1-x}\text{Ge}_x$ films from surface acoustic modes by Brillouin scattering 50 (1991) 265
- A. Baraldi, C. Ghezzi, A. Parisini, A. Bosacchi and S. Franchi, Analysis of electron mobility versus temperature after photoexcitation in Si-doped $\text{Al}_x\text{Ga}_{1-x}\text{As}$ 50 (1991) 303
- R. Nipoti, D. Pucci, A. Cetrionio and C. Lanzieri, Carrier and mobility profile measurements in n-type ion-implanted GaAs by the differential sheet resistivity and Hall effect technique 50 (1991) 405
- D.A. Woolf, D.I. Westwood, M.A. Anderson and R.H. Williams, The molecular beam epitaxial growth of $\text{GaAs}(\bar{1}\bar{1}\bar{1})/\text{Si}(111)$: a variable growth temperature study 50 (1991) 410
- B. Holländer, S. Mantl, B. Stritzker, F. Schäffler, H.-J. Herzog and E. Kasper, Strain and defect densities in Si/ $\text{Si}_{1-x}\text{Ge}_x$ heterostructures investigated by ion scattering and X-ray diffraction 50 (1991) 445
- R. Schwarz, T. Fischer, P. Hanesch, T. Muschik, J. Kolodzey, H. Cerva, H.L. Meyerheim and B.M.U. Scherzer, Limitations of interface sharpness in a-Si:H/a-SiC:H multilayers 50 (1991) 450
- H.-G. Hettwer, W. Lerch, B. Lentfort, N.A. Stolwijk and H. Mehrer, Combined application of spreading-resistance and electron-microprobe depth profiling on GaAs:Zn and Si:P 50 (1991) 456
- A. Castaldini, A. Cavallini, E. Gombia, R. Mosca and L. Tarricone, Evaluation of the diffusion length of minority carriers in bulk GaAs 50 (1991) 470
- 50 (1991) 485
- Silicon carbide*
- V.Kh. Kudoyarova, G.M. Gusinsky, L.A. Rassadin and I.V. Kudryavtsev, Hydrogen depth profile measurement in a- $\text{Si}_{1-x}\text{C}_x$:H films by elastic recoil detection 50 (1991) 173
- R. Schwarz, T. Fischer, P. Hanesch, T. Muschik, J. Kolodzey, H. Cerva, H.L. Meyerheim and B.M.U. Scherzer, Limitations of interface sharpness in a-Si:H/a-SiC:H multilayers 50 (1991) 456
- Silicon oxide*
- I.T. McGovern, Soft X-ray photoelectron spectroscopy of compound semiconductor surfaces and interfaces 50 (1991) 34
- G. Abstreiter, Micro-Raman spectroscopy for characterization of semiconductor devices 50 (1991) 73
- Sputtering*
- L.J. Bredell, F.D. Auret, G. Myburg and W.O. Barnard, Electrical characterization of argon-ion sputtered n-GaAs 50 (1991) 466
- Sulphides*
- C. Levade, J.J. Couderc, G. Vanderschaeve, D. Caillard and A. Couret, TEM in-situ observation of recombination-enhanced mobility of dislocations in II-VI compounds 50 (1991) 119
- A. Zakrzewski and M. Godlewski, Three-center Auger effect and the quantum yield of the luminescence of ZnS-based phosphors 50 (1991) 257
- C. De las Heras, I.J. Ferrer and C. Sánchez, Comparison of pyrite thin films obtained from Fe and natural pyrite powder 50 (1991) 505
- Superlattices*
- P.F. Fewster, Multicrystal X-ray diffraction of heteroepitaxial structures 50 (1991) 9
- C. Grattapain and A.M. Huber, Secondary ion mass spectrometry of dopants and impurities in compound semiconductors: depth profiling of homo- and heterostructure 50 (1991) 42
- J.H.C. Hogg, D. Shaw and D.M. Staudte, Modelling interdiffusion in epitaxial multilayer structures using X-ray simulation techniques 50 (1991) 87
- R. Zaus, M. Schuster, H. Göbel and J.-P. Reithmaier, Characterization of (In,

- GaAs/GaAs strained-layer multiple quantum wells with high-resolution X-ray diffraction and computer simulations 50 (1991) 92
- P. Auvray, A. Poudoulec, M. Baudet, B. Guenais, A. Regreny, C. d'Anter-roches and J. Massies, Interface roughness of GaAs/AlAs superlattices MBE-grown on vicinal surfaces 50 (1991) 109
- M. Mendik, M. Ospelt, H. von Känel and P. Wachter, Determination of elastic properties of Si/Ge superlattices and $\text{Si}_{1-x}\text{Ge}_x$ films from surface acoustic modes by Brillouin scattering 50 (1991) 303
- B. Jusserand and F. Molot, Confined optical vibrations: a new probe for alloy disorder 50 (1991) 317
- Surface and interface states*
- L. Roberts and G. Hughes, An investigation of metal/GaAs(100) interfaces by deep level transient spectroscopy 50 (1991) 424
- Surface phonons and adsorbate vibrations*
- M. Mendik, M. Ospelt, H. von Känel and P. Wachter, Determination of elastic properties of Si/Ge superlattices and $\text{Si}_{1-x}\text{Ge}_x$ films from surface acoustic modes by Brillouin scattering 50 (1991) 303
- Surface photovoltage*
- D. Lee, S.J. Barnett, A.D. Pitt, M.R. Houlton and G.W. Smith, Characterization of alloy composition in $\text{Ga}_{1-x}\text{Al}_x\text{As}$ /GaAs structures: comparison of photovoltage, X-ray, SIMS and RHEED techniques 50 (1991) 428
- A. Castaldini, A. Cavallini, E. Gombia, R. Mosca and L. Tarricone, Evaluation of the diffusion length of minority carriers in bulk GaAs 50 (1991) 485
- Surface roughness*
- P.F. Fewster, Multicrystal X-ray diffraction of heteroepitaxial structures 50 (1991) 9
- P. Auvray, A. Poudoulec, M. Baudet, B. Guenais, A. Regreny, C. d'Anter-roches and J. Massies, Interface roughness of GaAs/AlAs superlattices MBE-grown on vicinal surfaces 50 (1991) 109
- C. Frigeri, J.L. Weyher and M. De Potter, TEM study of the origin of the surface microroughness in DSL photoetched Si-implanted GaAs wafers 50 (1991) 115
- R.A.D. Mackenzie, J.A. Liddle and C.R.M. Grovenor, Ultrahigh resolution characterisation of compound semiconductors using pulsed laser atom probe techniques 50 (1991) 196
- Tin*
- B. Mari, A. Segura and A. Chevy, Electrical properties of neutron-transmutation-doped InSe 50 (1991) 415
- Titanium*
- P. Roura, J.R. Morante, G. Bremond, T. Benyattou, G. Guillot and W. Ulrici, Complete identification of the Ti-related levels in GaP 50 (1991) 496
- X-ray diffraction*
- J. Matsui, Study of strain variation in LEC-grown GaAs bulk crystals by synchrotron radiation X-ray topography 50 (1991) 1
- P.F. Fewster, Multicrystal X-ray diffraction of heteroepitaxial structures 50 (1991) 9
- J.H.C. Hogg, D. Shaw and D.M. Staudte, Modelling interdiffusion in epitaxial multilayer structures using X-ray simulation techniques 50 (1991) 87
- R. Zaus, M. Schuster, H. Göbel and J.-P. Reithmaier, Characterization of (In, Ga)As/GaAs strained-layer multiple quantum wells with high-resolution X-ray diffraction and computer simulations 50 (1991) 92
- N. Herres, G. Bender and G. Neumann, Assessment of mismatched epitaxial layers by X-ray rocking curve measurements and simulations 50 (1991) 97
- A.M. Keir, S.J. Barnett, J. Giess, T.D. Walsh and M.G. Astles, A combination of high-resolution X-ray diffractometry and diffraction imaging techniques applied to the study of MOVPE-grown $\text{Cd}_x\text{Hg}_{1-x}\text{Te}$ /CdTe on GaAs 50 (1991) 103
- P. Auvray, A. Poudoulec, M. Baudet, B. Guenais, A. Regreny, C. d'Anter-roches and J. Massies, Interface

- roughness of GaAs/AlAs superlattices MBE-grown on vicinal surfaces
P.L. Swart, B.M. Lacquet and R. Thavar, Physical characterization of OMVPE-grown $\text{Al}_x\text{Ga}_{1-x}\text{As}$ multi-layer films by means of non-destructive optical reflectometry 50 (1991) 109
- S.C. Moss, J.F. Knudsen, R.C. Bowman, Jr., P.M. Adams and D.D. Smith, Picosecond transient photoreflectance measurements of ion-implanted GaAs 50 (1991) 330
- D. Lee, S.J. Barnett, A.D. Pitt, M.R. Houlton and G.W. Smith, Characterization of alloy composition in $\text{Ga}_{1-x}\text{Al}_x\text{As}/\text{GaAs}$ structures: comparison of photovoltage, X-ray, SIMS and RHEED techniques 50 (1991) 337
- D. Ashenford, J.H.C. Hogg, B. Lunn and C.G. Scott, The relationship between electrical and structural characteristics of CdTe and CdMnTe layers grown on InSb 50 (1991) 428
- D.A. Woolf, D.I. Westwood, M.A. Anderson and R.H. Williams, The molecular beam epitaxial growth of $\text{GaAs}(\overline{111})/\text{Si}(111)$: a variable growth temperature study 50 (1991) 440
- B. Holländer, S. Mantl, B. Stritzker, F. Schäffler, H.-J. Herzog and E. Kasper, Strain and defect densities in $\text{Si}/\text{Si}_{1-x}\text{Ge}_x$ heterostructures investigated by ion scattering and X-ray diffraction 50 (1991) 450
- R. Schwarz, T. Fischer, P. Hanesch, T. Muschik, J. Kolodzey, H. Cerva, H.L. Meyerheim and B.M.U. Scherzer, Limitations of interface sharpness in a-Si:H/a-SiC:H multilayers 50 (1991) 456
- C. De las Heras, I.J. Ferrer and C. Sánchez, Comparison of pyrite thin films obtained from Fe and natural pyrite powder 50 (1991) 505

Zinc

- J.G. Bauer, R. Treichler, T. Hillmer, J. Müller and G. Ebbinghaus, Optimization of Zn dopant profiles in a pin-diode/FET by combination of depth profiling techniques: a SIMS, ECV and AES study 50 (1991) 138
- A.W.R. Leitch, Th. Prescha and M. Stutzmann, Hydrogen passivation and reactivation of shallow Zn acceptors in GaAs 50 (1991) 390
- H.-G. Hettwer, W. Lerch, B. Lentfort, N.A. Stolwijk and H. Mehrer, Combined application of spreading-resistance and electron-microprobe depth profiling on GaAs:Zn and Si:P 50 (1991) 470